

Nanophotonic Structures for Control of Light-matter Interaction

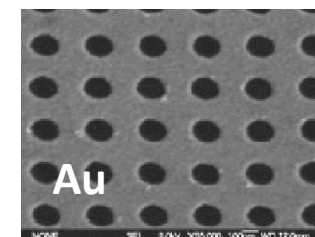
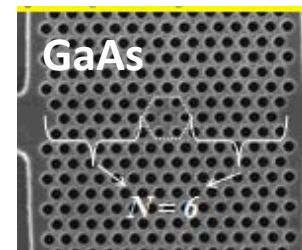
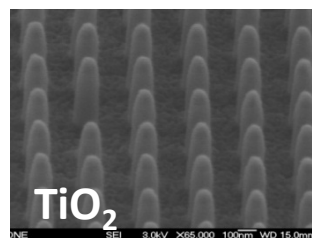
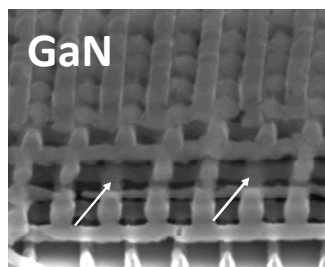
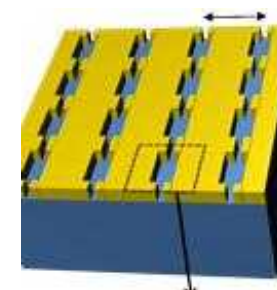
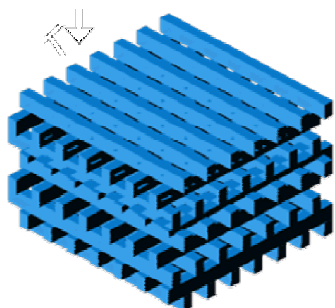
Ganapathi Subramania

Advanced Material Science 01126

Sandia National Laboratories, Albuquerque, NM

Indian Institute of Technology, Kanpur, India

August 16-17, 2013



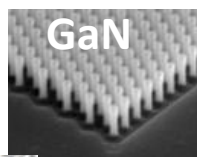
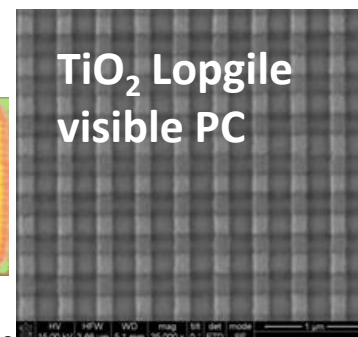
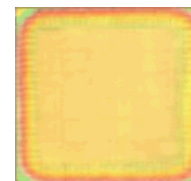
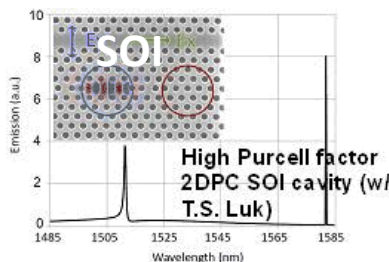
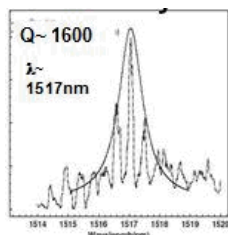
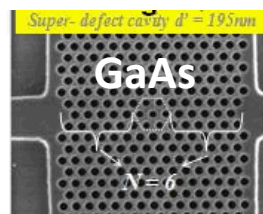
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Acknowledgements

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- Jon Wierer
- Sheng Liu
- Alex Benz
- John Nogan
- Doug Pete
- Carlos Sanchez
- Tony Coley
- Travis Young
- Luke Lester
- Stavroula Foteinopoulou
- Bob Biefeld
- Jerry Simmons

Nanophotonics Activity

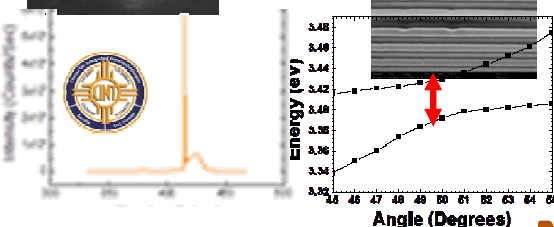
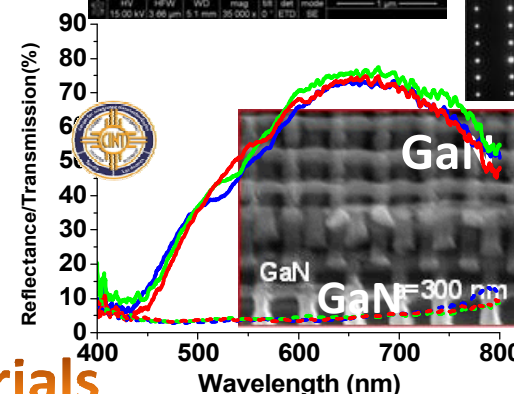
Integrated Photonics, Nanoscale lasing, Strong coupling, Full 3D emission control, Thermal control, Solid State lighting, Energy conversion



Strong coupling (w/A. Fischer)

1,2D PC 3D PC

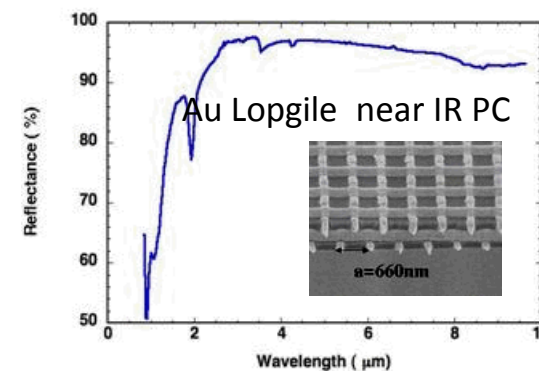
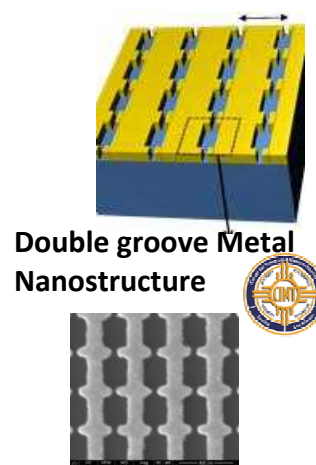
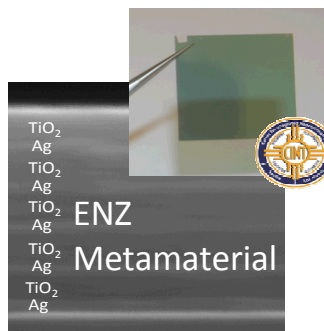
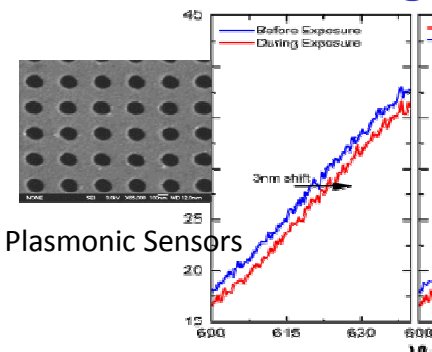
Photonic Nanostructures



GaN 2DPC laser w/ G. Wang, I. Brener

Metal optics and Metamaterials

Ultrasubwavelength light control, Detection, Sensing, Nanocircuitry



Energy Frontier Research Center for Solid-State-Lighting Science

- **Duration: Aug 2009 – Jul 2014**
- **One of 46 EFRC centers nationwide**
- **Budget: \$3.6M/year for 5 years**

Director:

Mike Coltrin

Chief Scientist:

Jeff Tsao



Senior Staff

Jerry Simmons

Andy Armstrong

Normand Modine

Weng Chow

Dan Koleske

Ken Lyo

Jianyu Huang

Francois Leonard

Jim Martin

Lauren Rohwer

May Nyman

Igal Brener

Willie Luk

Ganesh Subramania

Eric Shaner

Post-Docs and

Students

Jeremy Wright

Business Staff

Rene Sells

Jessica Hobbs

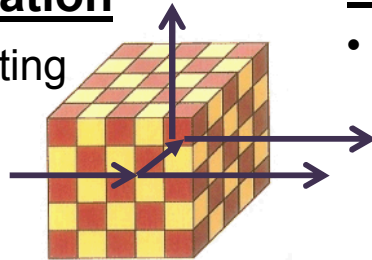
Denise LaPorte

Luz Tirado

3D PC: A Great Platform for Light Manipulation

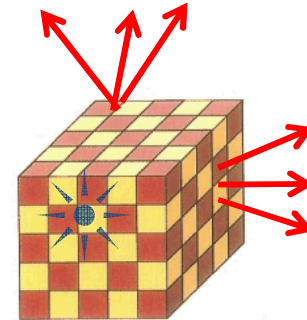
Control of light propagation

- Guiding, bending and splitting
- Negative refraction
- Self-collimation
- Localization
- Slow light
- Cloaking

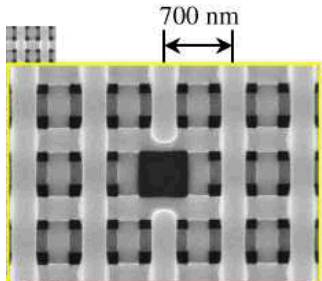


Control of light emission

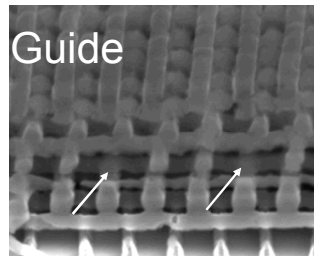
- Full 3D confinement effect
 - Photon – Atom Bound states,
 - Non-Markovian emission process



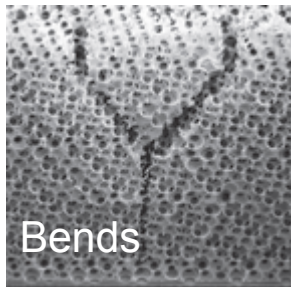
- Photonic Density of States effect
 - Spontaneous emission enhancement



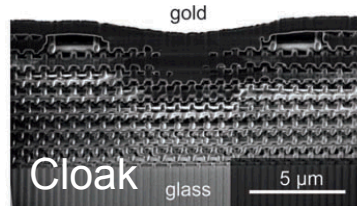
S. Kawashima et. al., Opt. Exp. **18**, 386 (2010)



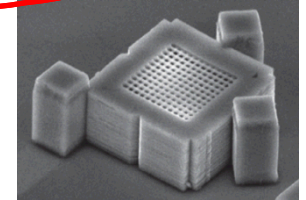
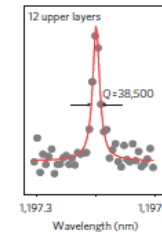
G. Subramania et. al, Nano Lett. **11**, 4591 (2011).



S.A. Rinne et. al., Nat. Phot. **2**, 52(2008)

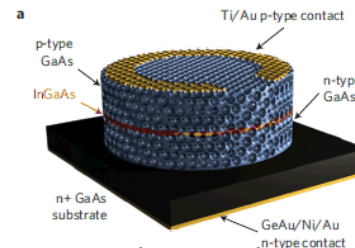


T. Ergin et. al., Science **328**, 337 (2010)



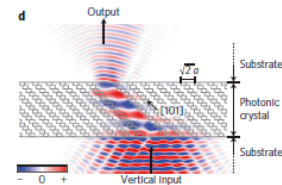
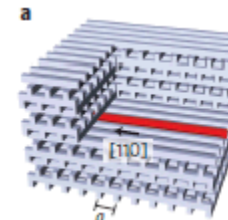
A. Tandraechanurat et. al., Nat Photon **5**, 91 (2011).

Electrical Injection



E. C. Nelson, et al., Nat Mat **10**, 676 (2011)

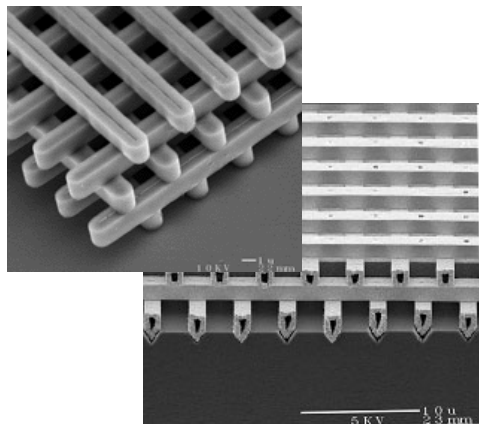
Emission enhancement



K. Ishizaki et.al. , Nat. Phot., **7**, 133 (2013)).

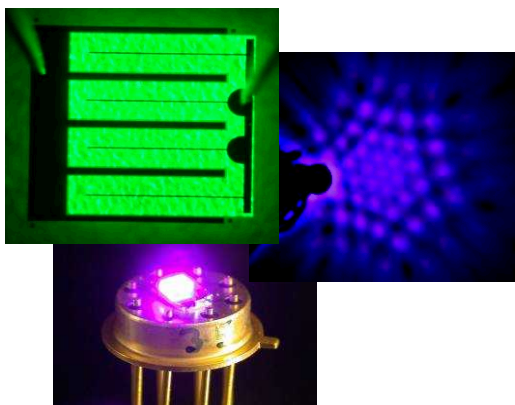
Objective : Understand Spontaneous Emission Control to Benefit SSL

3D photonic crystals

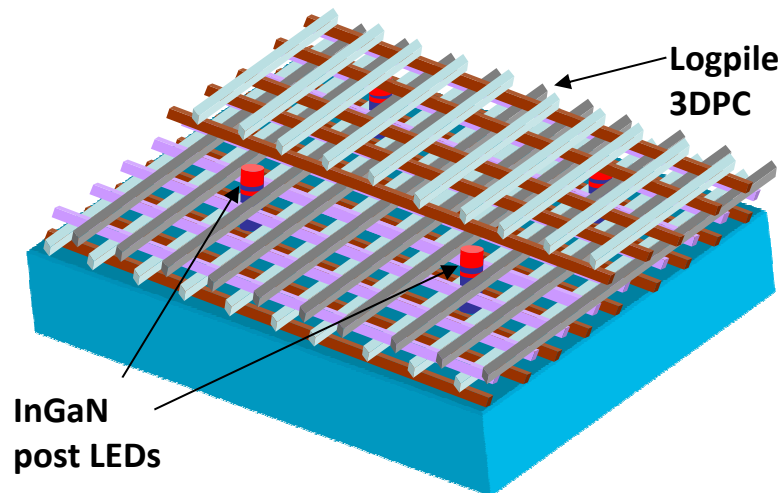


- Sandia has strong capabilities in 3DPC and Nitrides
- Merge InGaN LED research with 3D photonic crystal research.

InGaN LEDs



InGaN LED array incorporated into a 3DPC



Improving InGaN LED efficiency enhancements will benefit SSL – e.g. Green emission.

Spontaneous Emission Control using PC

Radiative rate of an emitting dipole in an EM field
(Fermi's Golden Rule)

$$\Gamma_r(\omega) = \frac{\pi\omega\mu^2}{3\varepsilon_0\hbar} \rho(\omega)$$

Photonic Density of States (PDOS)

$$\rho_f(\omega) = \frac{\omega^2}{\pi^2 c^3} \quad \leftarrow \text{PDOS in free space}$$

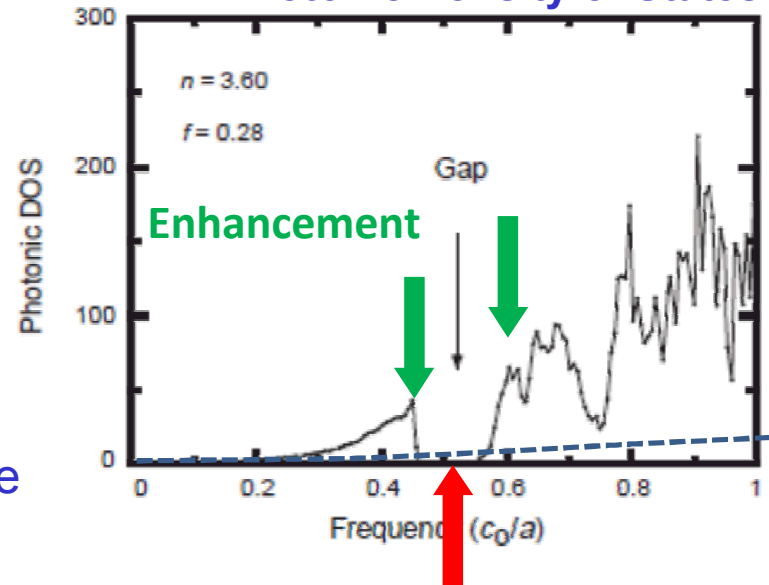
Radiative rate
modification

$$\frac{\Gamma_{r_PC}(\omega)}{\Gamma_{r_free}(\omega)} = \frac{\rho_{PC}(\omega)}{\rho_f(\omega)}$$

Local Photonic Density of States (LDOS)

$$\rho_L(\mathbf{r}, \omega) = \sum_n \int_{1stBZ} d^3k |\bar{\boldsymbol{\mu}} \cdot \mathbf{E}_{n,k}(\mathbf{r})|^2 \delta(\omega^2 - \omega_{n,k}^2)$$

PC Photonic Density of States



Also Important :

- Where the emitters are located in the unit cell
- The orientation of the emitter dipole w.r.t to the eigenfield

Visible Frequency Logpile Photonic Crystal

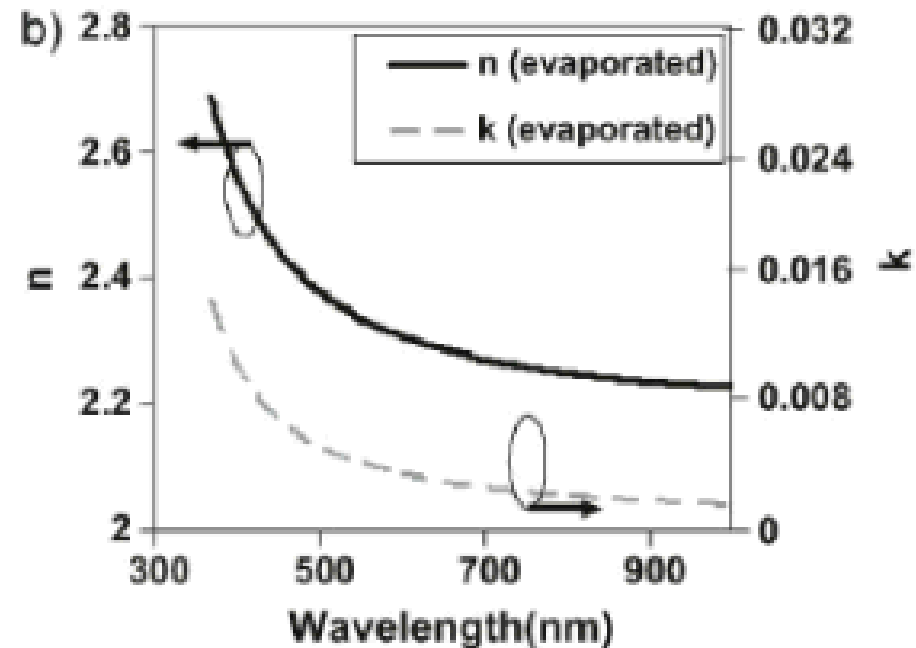
Material Choice : TiO_2

Requirements:

- High enough index with low loss in the visible :
 - $n \sim 2.3\text{-}2.4$ in the visible /w $k < 0.015$
- Easy to deposit :
 - Sputtering, evaporation, solgel, Atomic Layer Deposition

Method of fabrication:

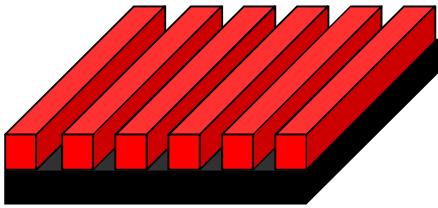
- Nanofabrication based on electron beam lithography



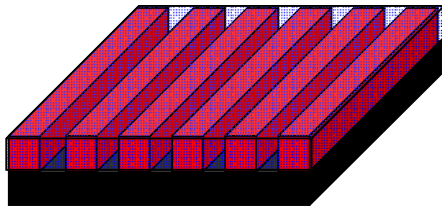
Multilevel E-beam Fabrication Process

PC fabricated one layer at a time.

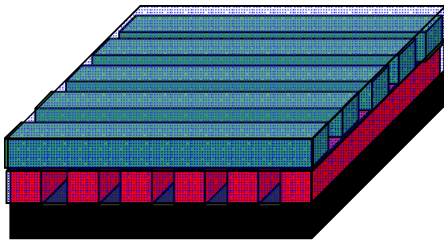
1. Fabricate first level



2. Fill and planarize



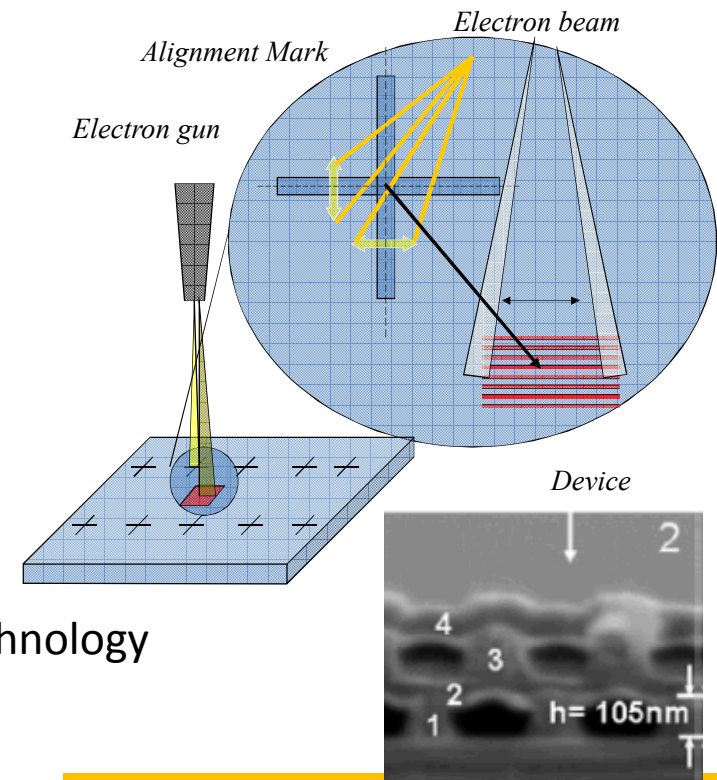
3. Make next level



4. Repeat process to make additional levels

Alignment

- Lattice constants $< 400\text{nm}$
- Alignment precision to within 10% of lattice constant needed
- High quality Au registration marks



- Alignment
- Planarization

G. Subramania, Nanotechnology
18, 035303 (2007).

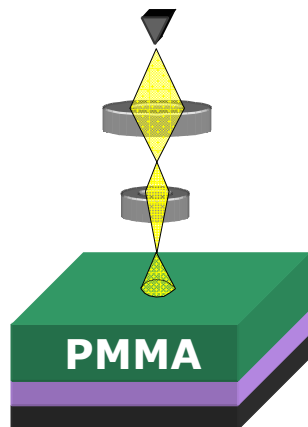
Excellent alignment was obtained
with both JEOL- JBX5E and 9300FS

TiO₂ Logpile Photonic Crystal Fabrication Process

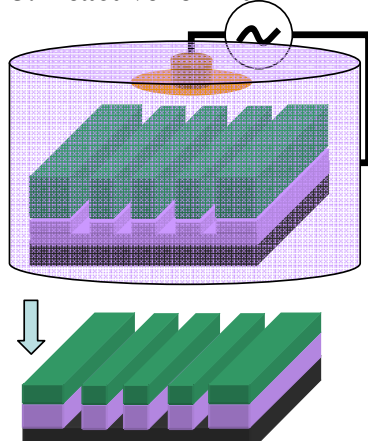
1. Deposit SiO₂



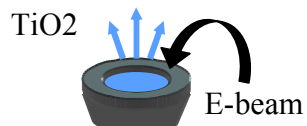
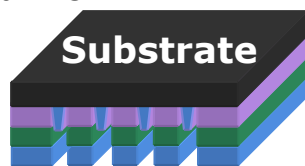
2. E-beam Write



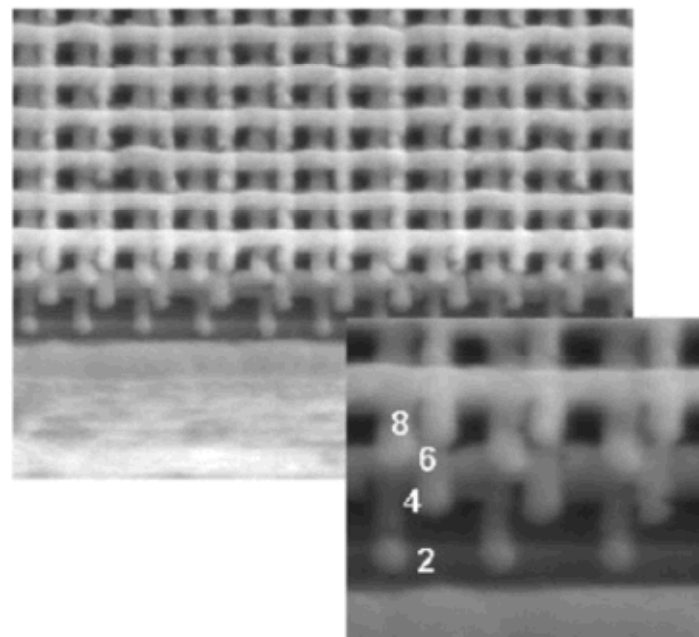
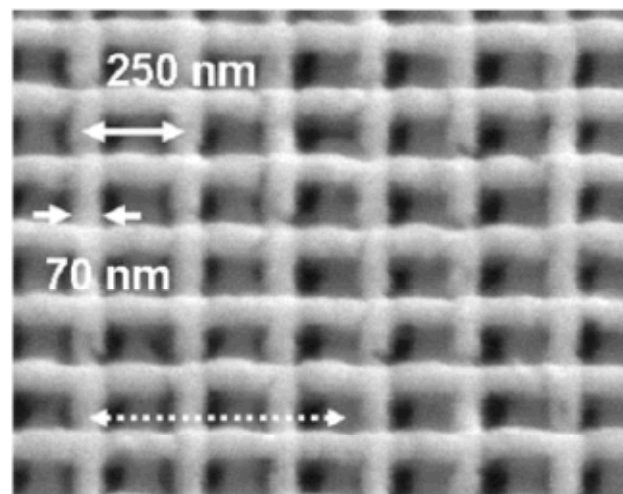
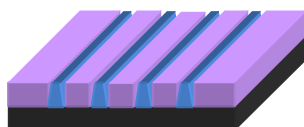
3. Reactive-ion Etch



4. E-beam evaporation of TiO₂

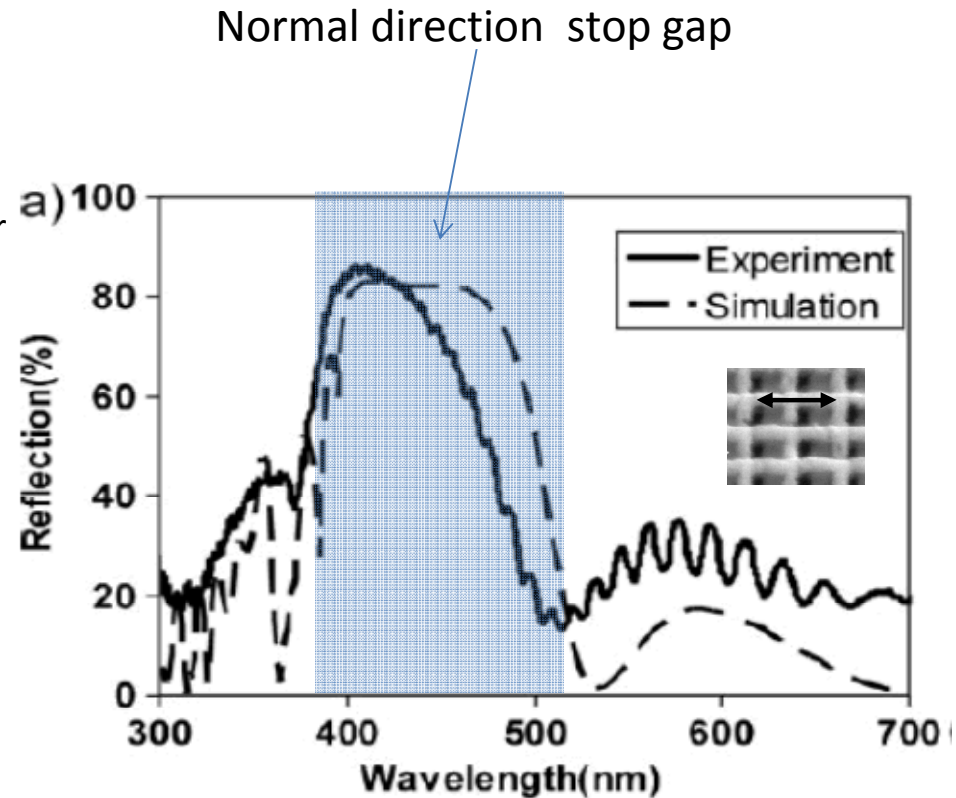
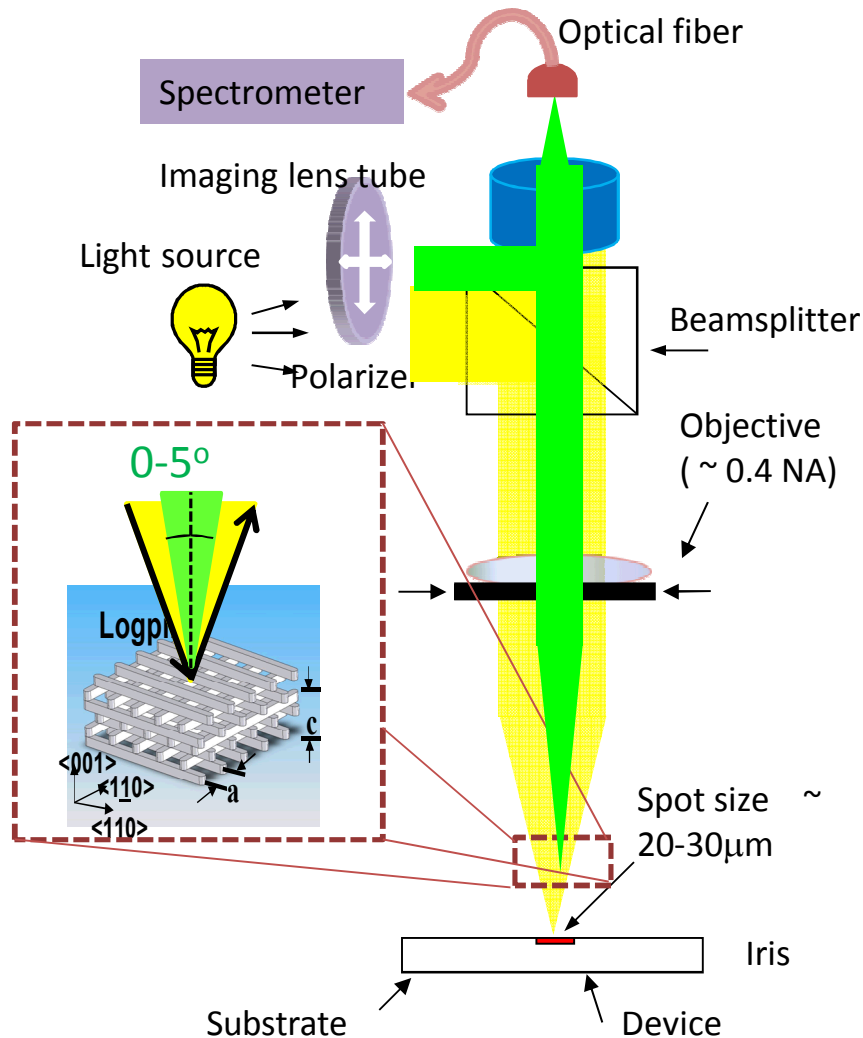


5. Post lift-off



G. Subramania et. al., Adv. Mat. **22**, 487-491 (2010)

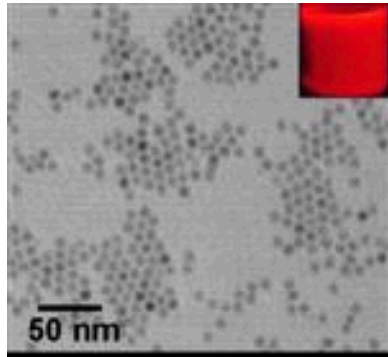
Visible- Near UV 9 Layer TiO_2 Logpile



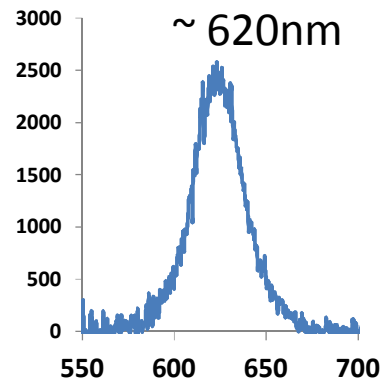
G. Subramania, Y.-J. Lee, A. J. Fischer, and D. D. Koleske, *Advanced Materials* **22**, 487-491 (2010)

Emission Modification in TiO_2 Logpile

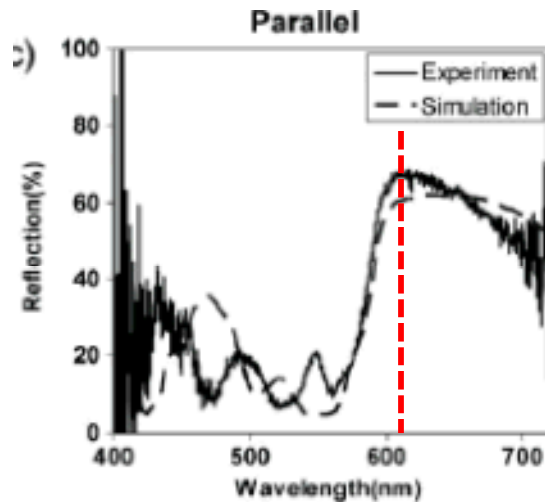
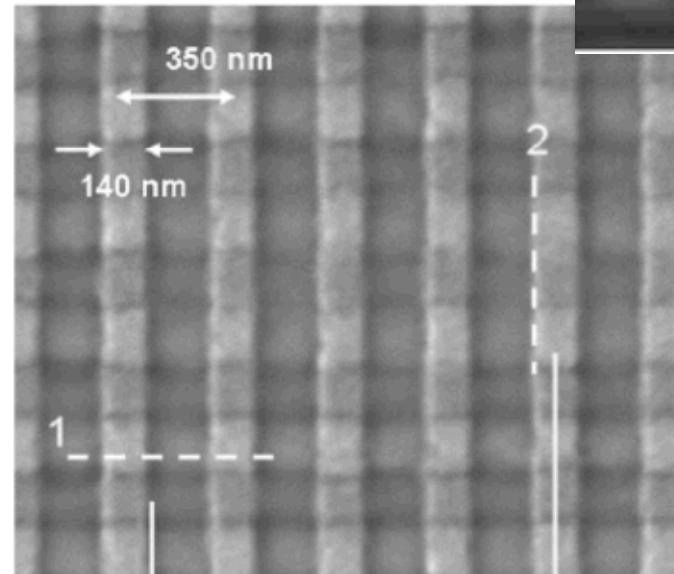
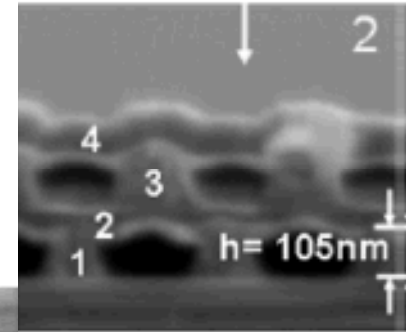
CdSe red emitting quantum dots



(www.nn-labs.com)



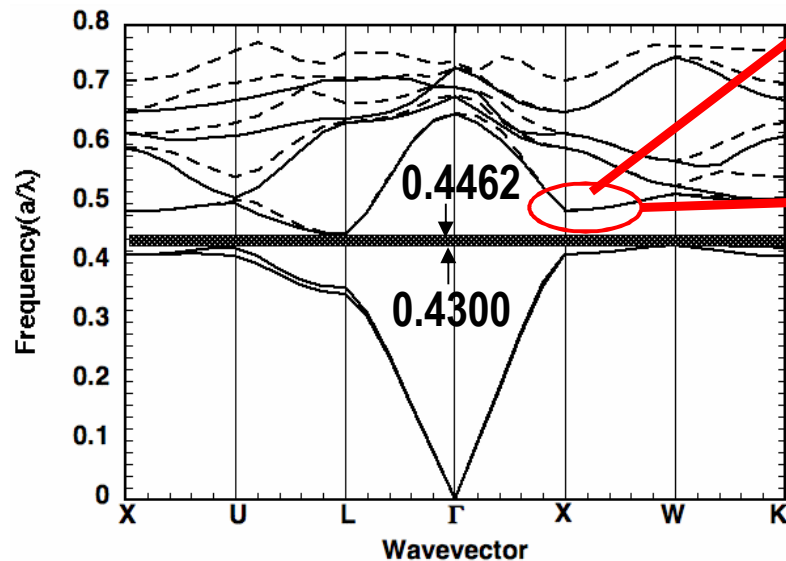
Larger lattice constants $a = 350, 400$ with 4 Layers



G. Subramania, Y. J. Lee, A. J. Fischer, T. S. Luk, C. J. Brinker, D. Dunphy, Appl. Phys. Lett. , **95**, 151101(2009)

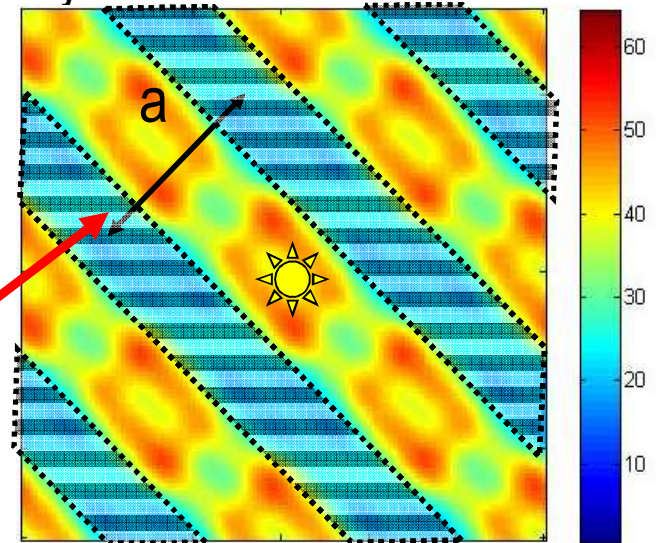
Effect of LDOS- Emitter Placement Inside the PC

- Thus far emission control studies typically done for emitters in high index region – probing dielectric band
- Effect of ‘air band’ modes have not been probed
- Advantages
 - Post introduction of light source
 - Choice of light source (QDs or dyes or gas)
 - Potentially higher density of states enhancement

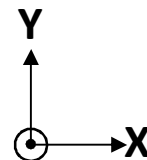
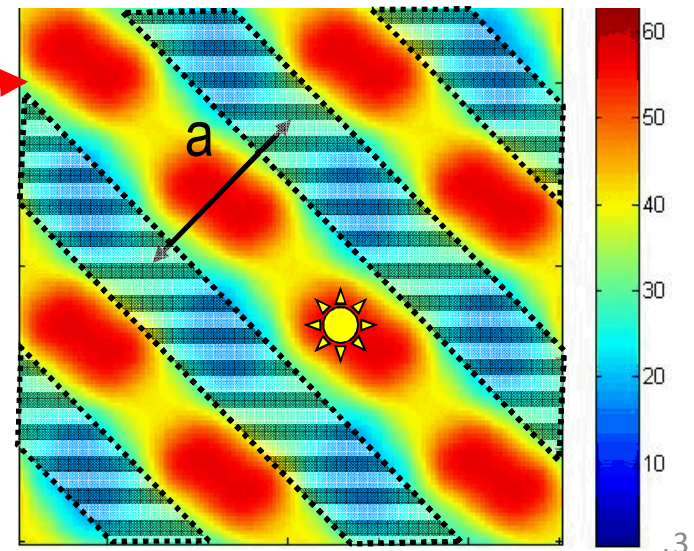


Field Distribution for the ‘air band’ using PWE method

E_y field distribution at Xpt



E_z field distribution at Xpt



Requirements for Accessing the 'Air' Void Region of the PC

- **Key Challenge:** Locating the QDs in the void region without affecting the photonic bandgap
- Physical access to the 'air' region with ability to attach QDs
- Low refractive index: minimal disturbance to photonic bandgap

Room temperature Spin Coatable Aerogel

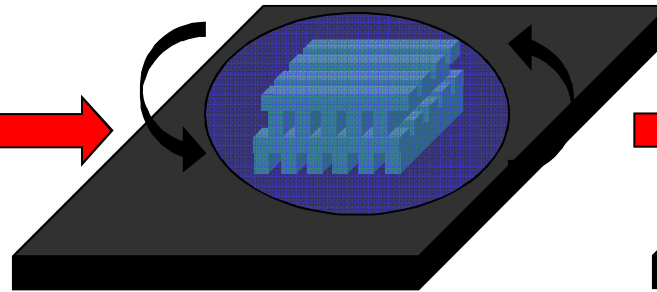
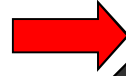
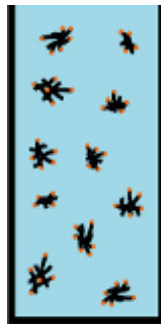
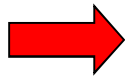
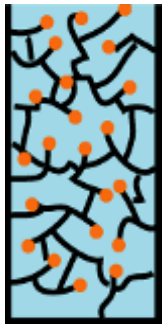
Brinker group (S. S. Prakash et al.,
Nature **374**, 439 (1995))

Age and
cap gel

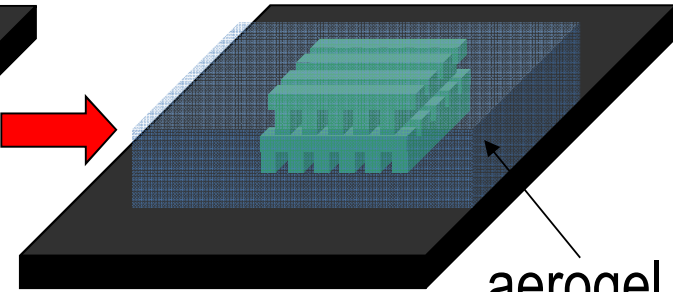
Disperse by
sonication

Spin coat

dry at RT



Logpile PC



Logpile PC

aerogel

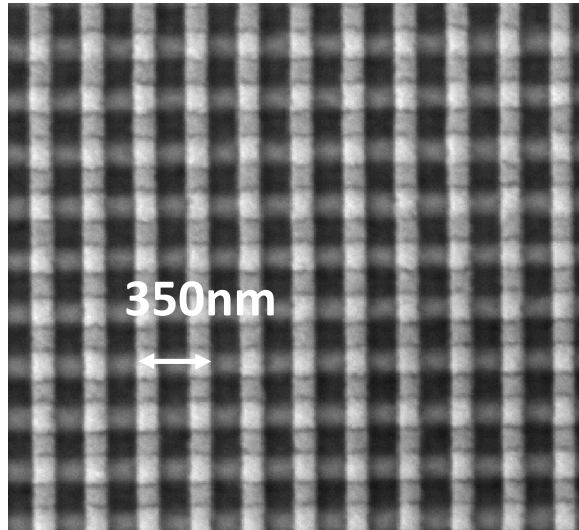
Introduce QDs through chemical attachment (3-mercaptopropyltrimethoxysilane chemistry)

Developed by
Alex Lee

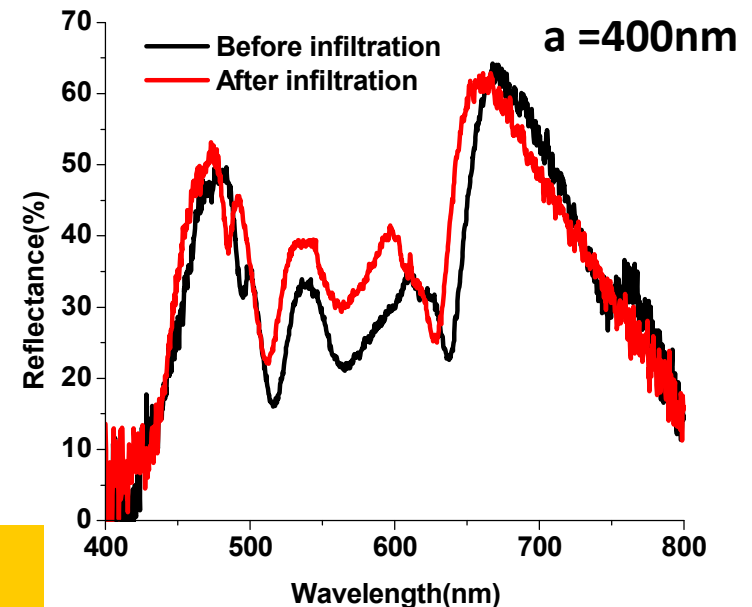
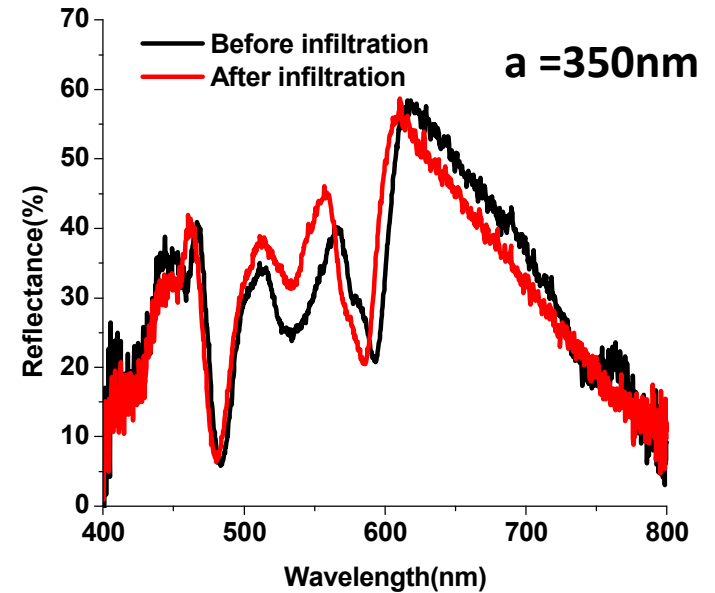
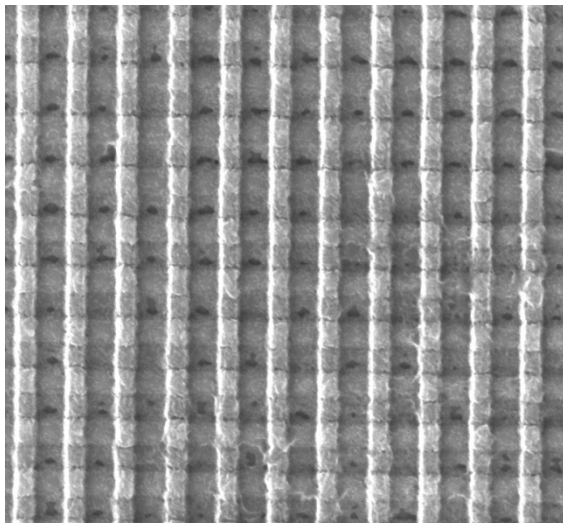
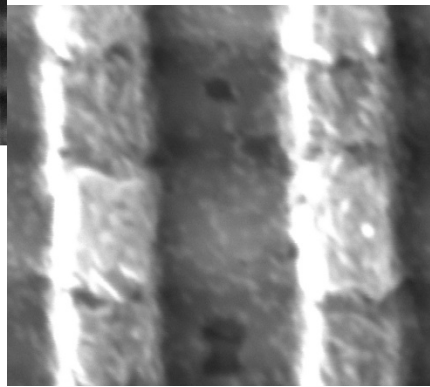


G. Subramania, Y. J. Lee, A. J. Fischer, T. S. Luk, C. J. Brinker, D. Dunphy, Appl. Phys. Lett. , **95**, 151101(2009)

Effect of Aerogel and CdSe QD infiltration

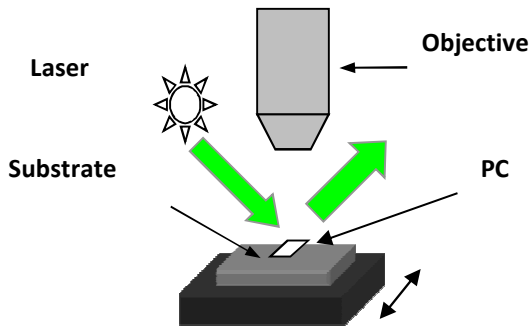


Aerogel Ref. index
 $\sim 1.05-1.1$



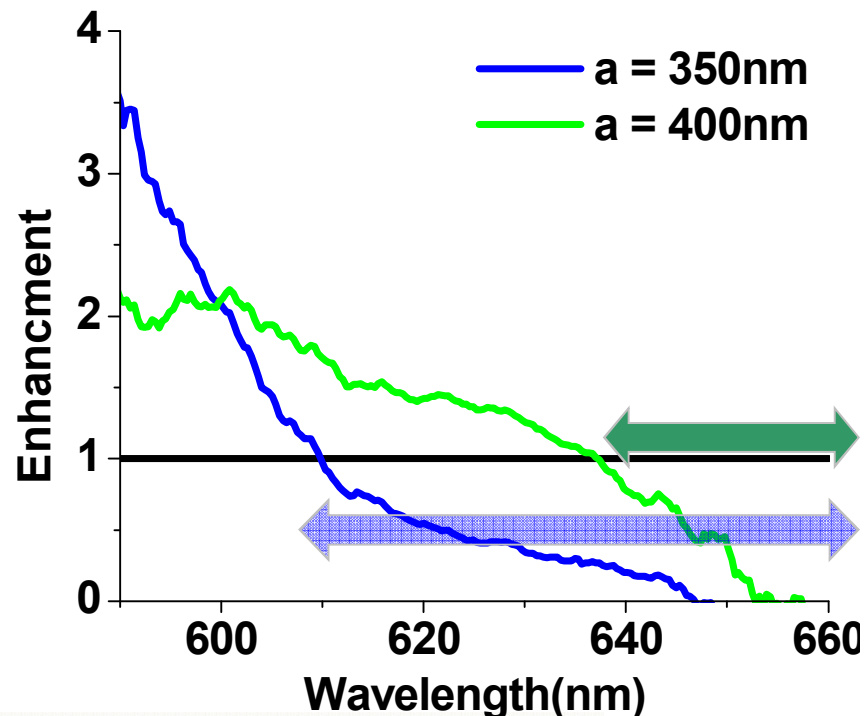
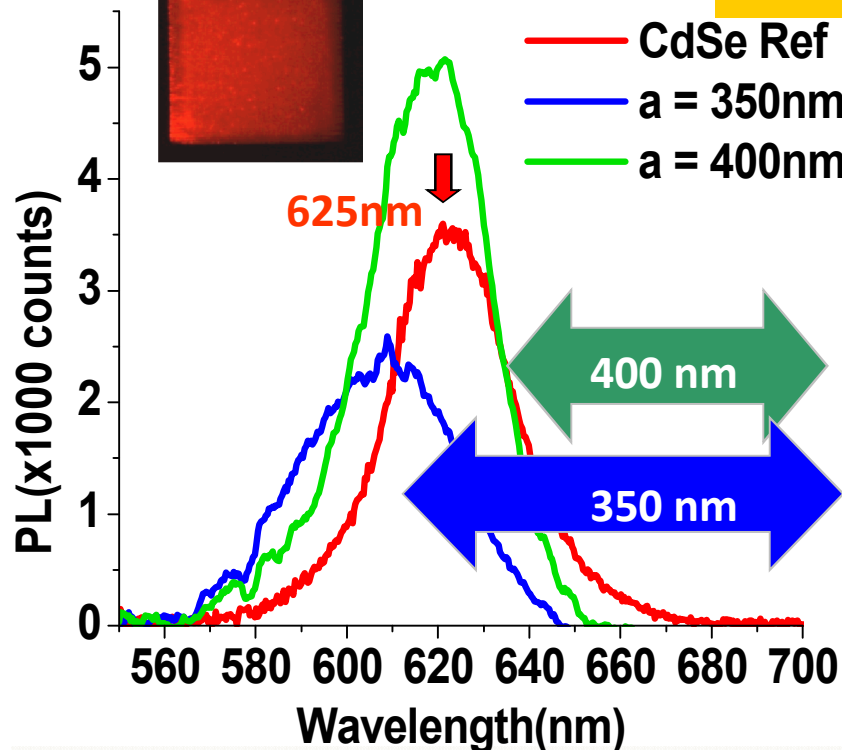
Aerogel and CdSe QD infiltration has negligible effect on the bandgap!

Spontaneous Emission Modification



- Microphotoluminescence with 532nm (5mW CW pump)
- Equivalent volume of unpatterned CdSe infiltrated aerogel as reference

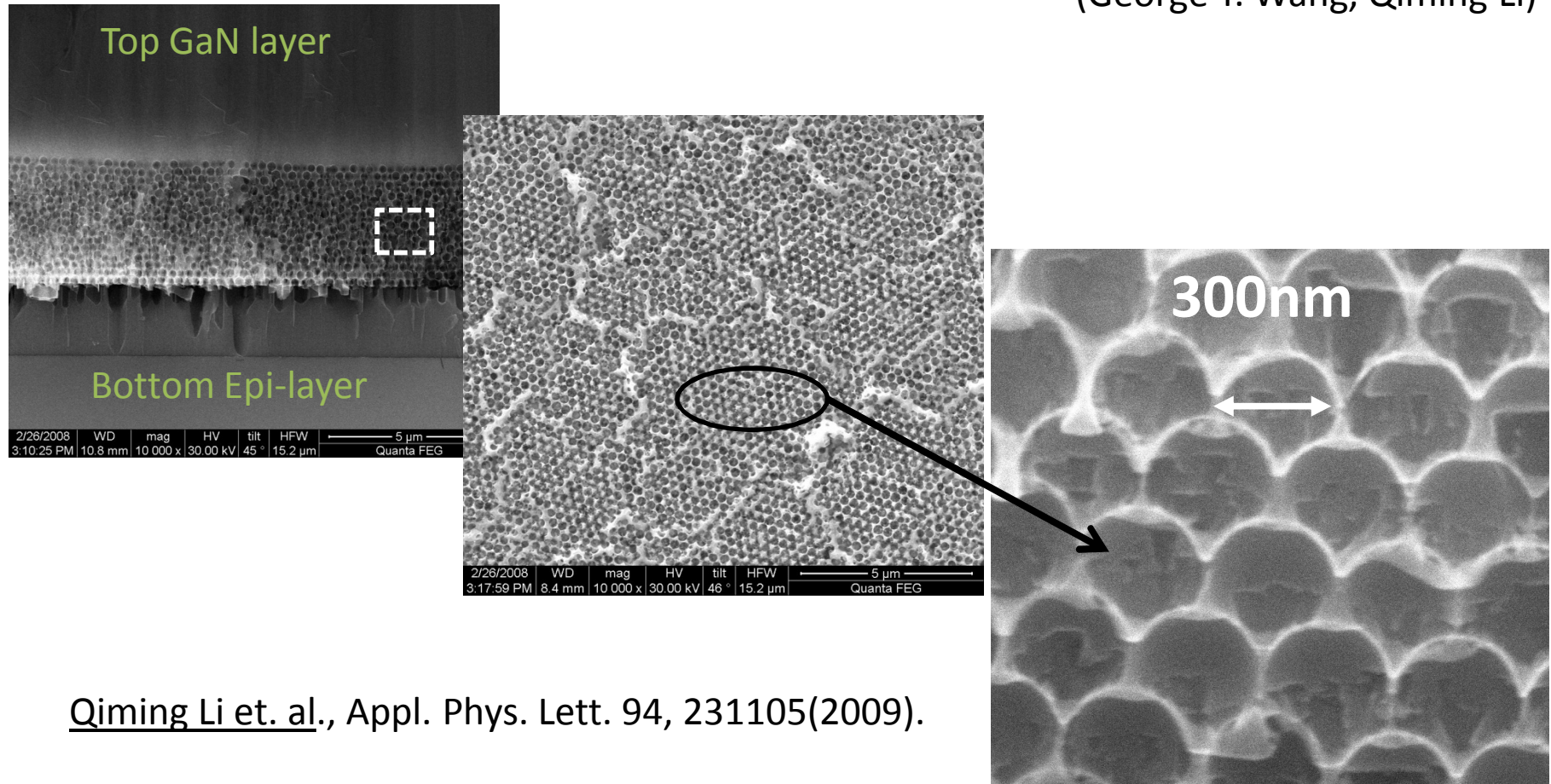
Light emission suppression inside the bandgap and enhancement at the band edge



G. Subramania, Y. J. Lee, A. J. Fischer, T. S. Luk, C. J. Brinker, D. Dunphy, Appl. Phys. Lett. , **95**, 151101(2009)

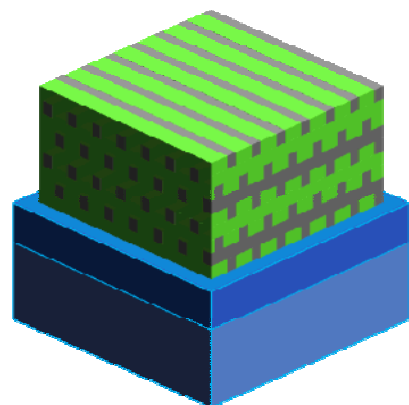
Epitaxial GaN grown though nanostructured template reduces dislocation density

(George T. Wang, Qiming Li)

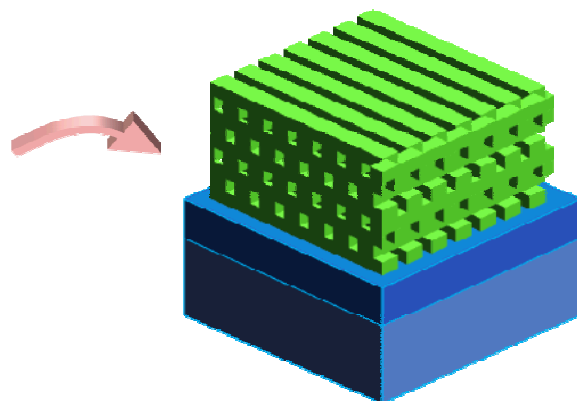


Qiming Li et. al., Appl. Phys. Lett. 94, 231105(2009).

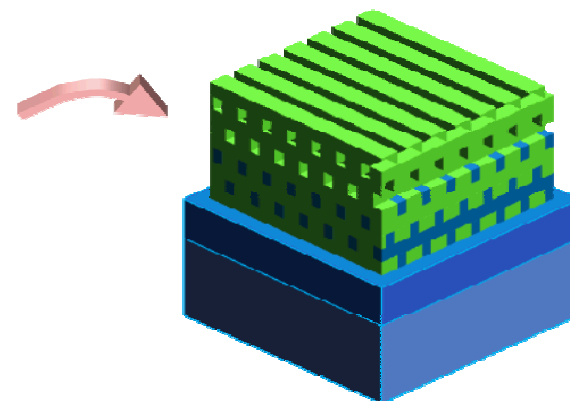
GaN growth through logpile template



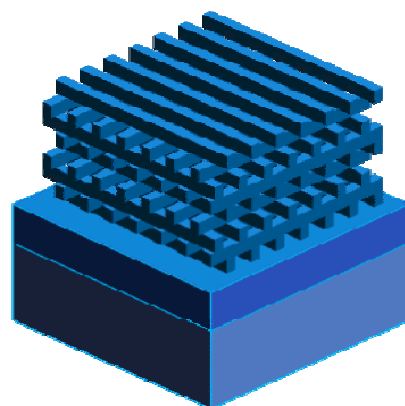
1. Si/SiO₂ logpile PC



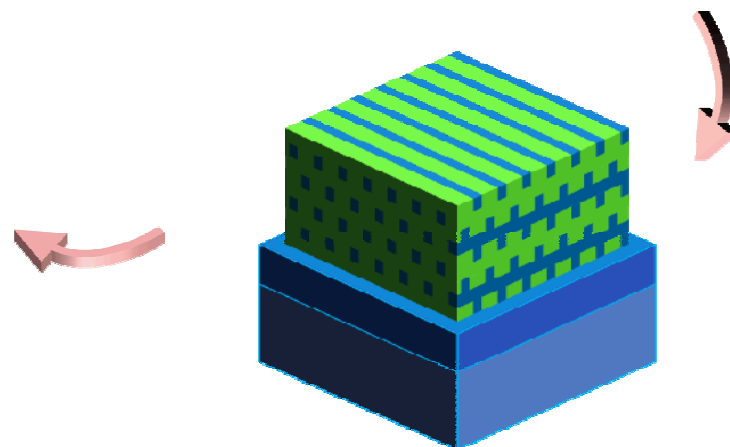
2. After Si is removed with KOH.



3. MOCVD GaN growth through SiO₂ template

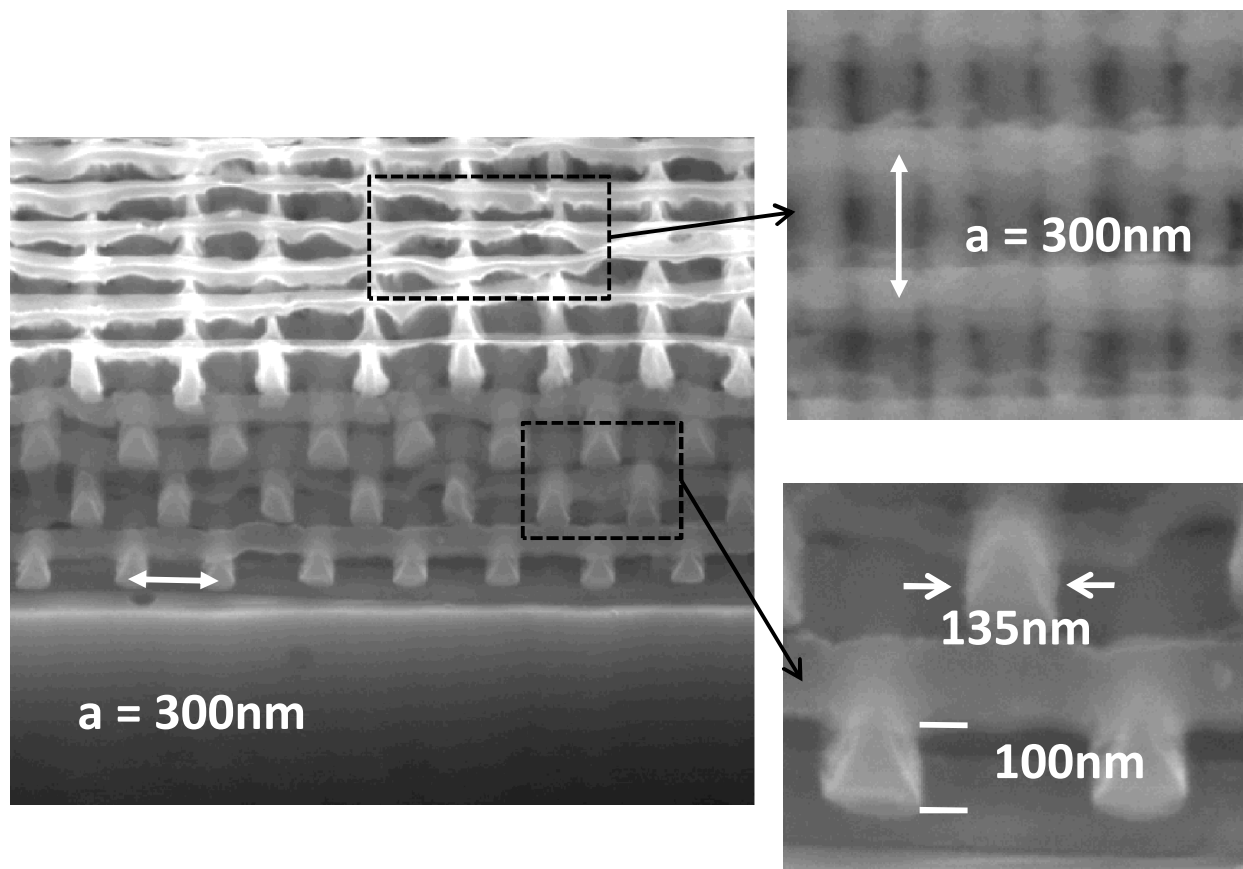


5. GaN logpile PC after SiO₂ logpile template removal



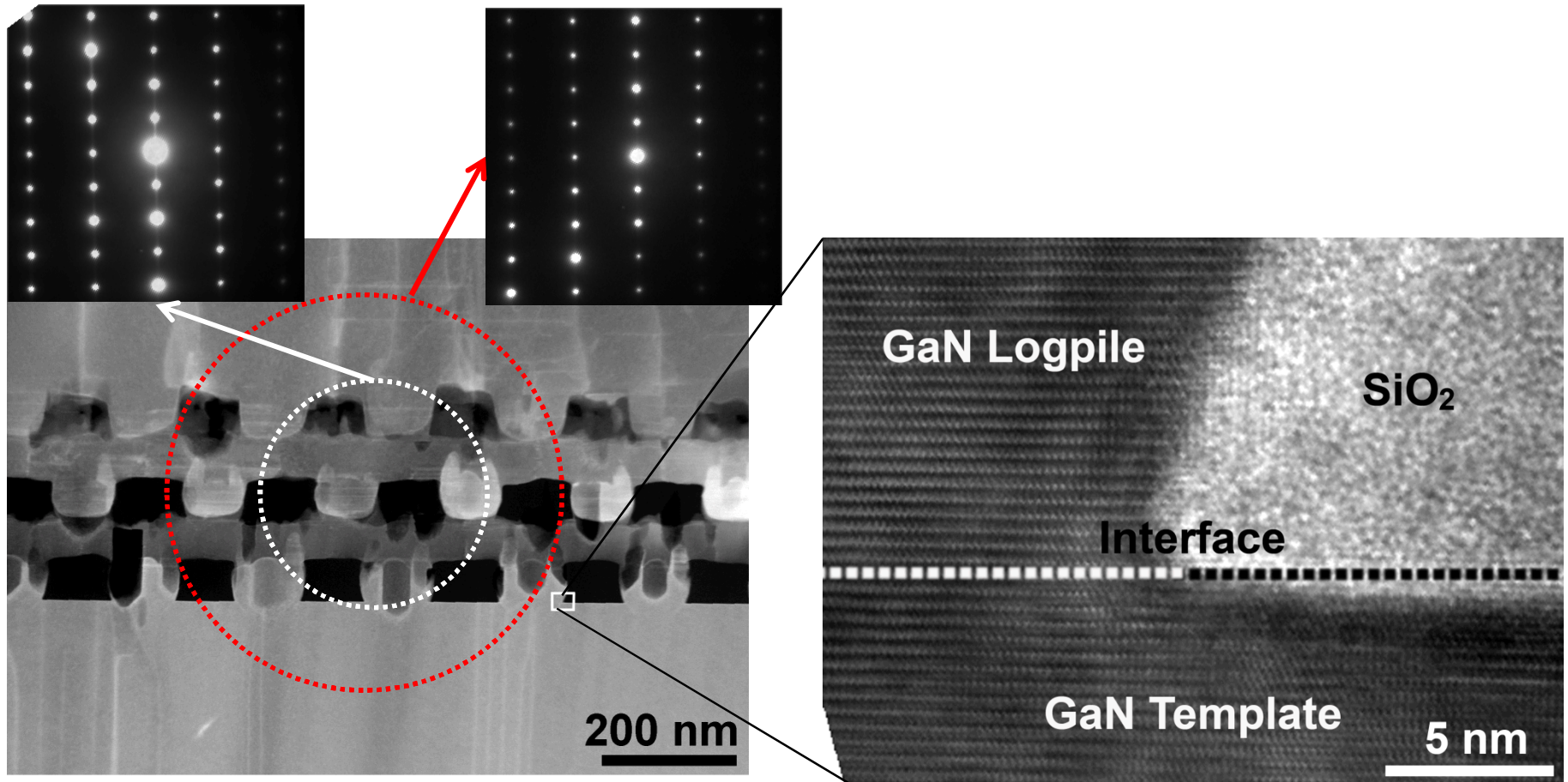
4. After complete GaN infiltration into SiO₂ logpile template

A nine layer all GaN logpile PC



G. Subramania, Q. Li, Y.-J. Lee, J. J. Figiel, G. T. Wang, and A. J. Fischer, Nano Lett. **11**, 4591 (2011).

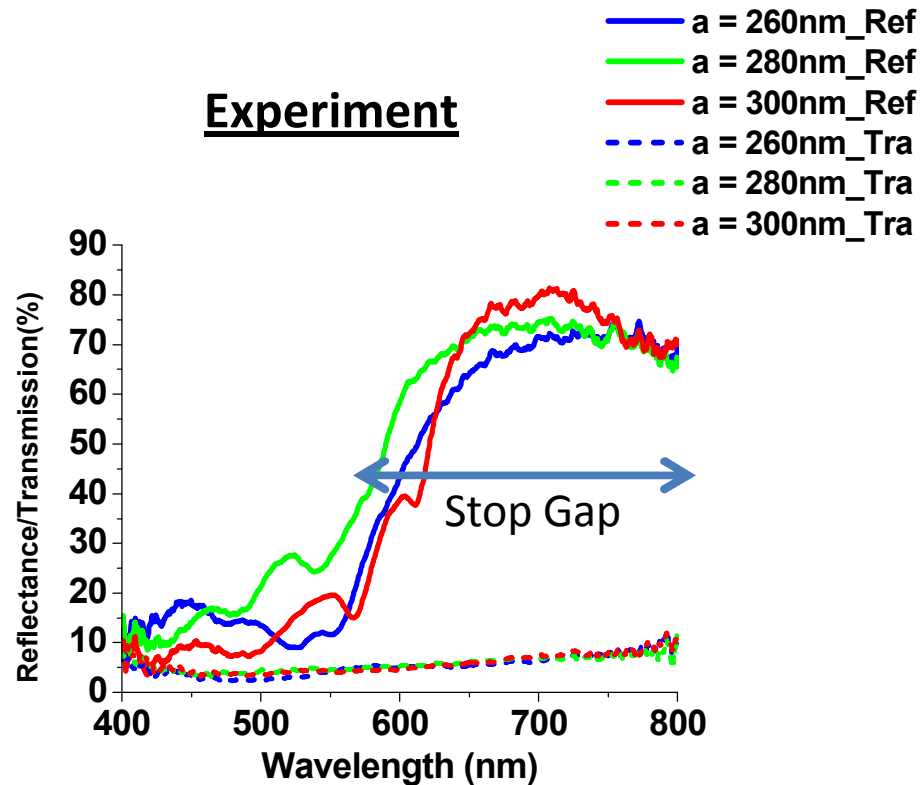
Bottom-up epitaxial growth of crystalline GaN



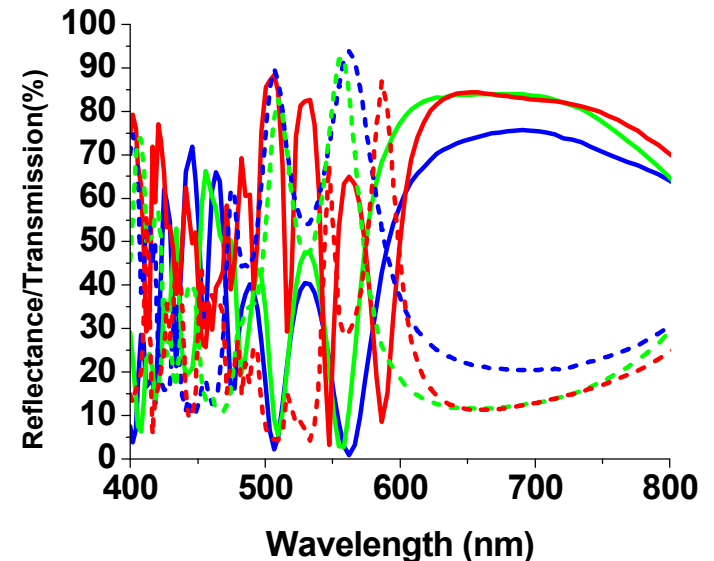
G. Subramania et. al. , Nano Lett. **11**, 4591 (2011).

Optical Response

Experiment



FDTD Simulation



G. Subramania et. al. , Nano Lett. **11**, 4591 (2011).

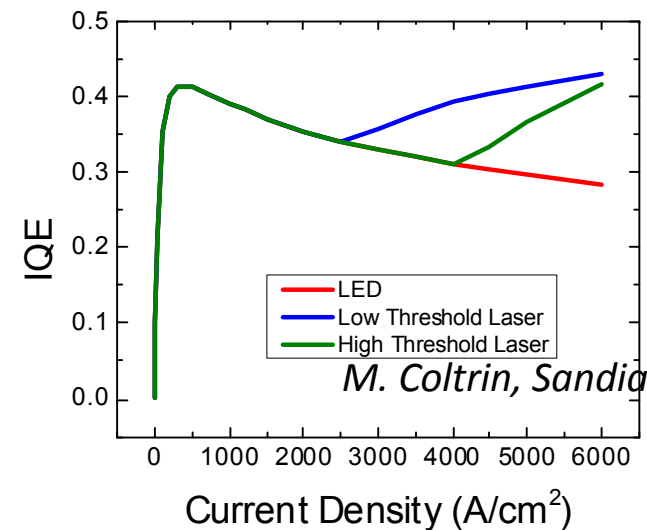
Nanowire Photonic Crystal Lasers

(Jeremy B. Wright, Sheng Liu, Alexander Benz, George T. Wang, Qiming Li, Daniel D. Koleske, Ping Lu, Huiwen Xu, Luke Lester, Ting S. Luk, Igal Brener)

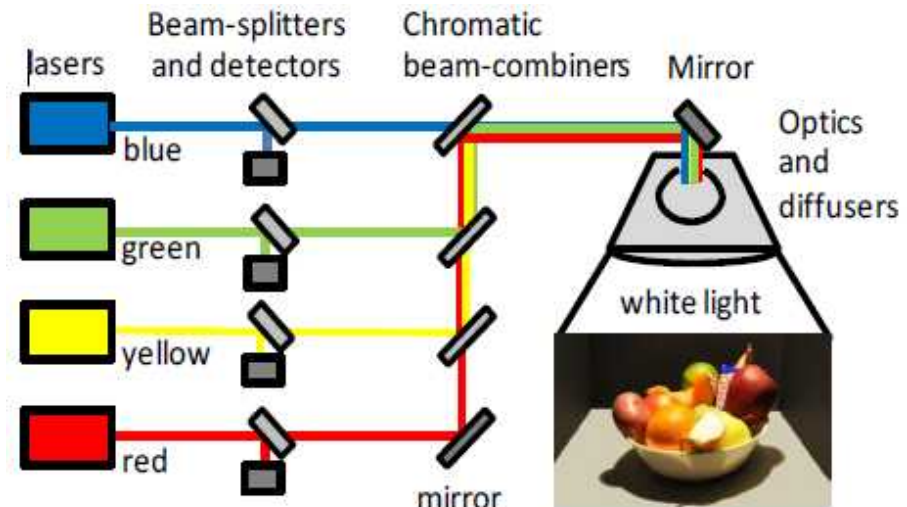
Why Lasers in Solid State Lighting?

The LED “efficiency droop” problem:

- InGaN LEDs exhibit a decrease in efficiency at high drive currents*
- limits the operating current density*
- increases the cost per lumen*



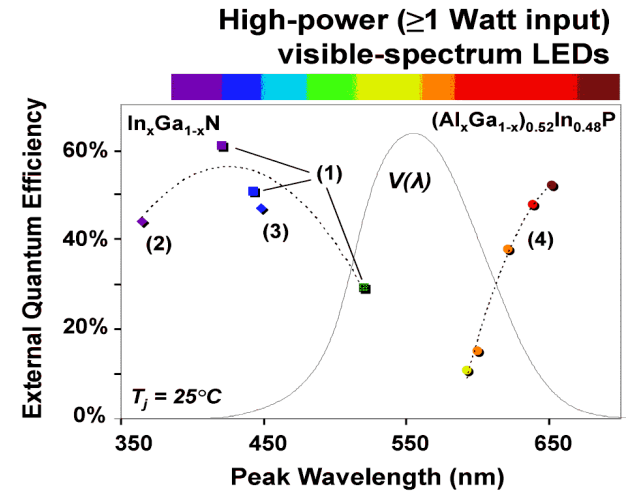
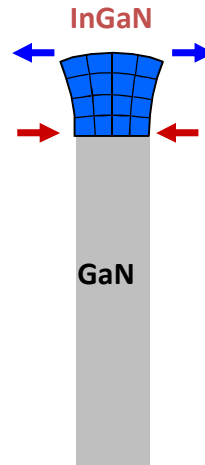
- *4 color lasers suitably combined can achieve high color rendering*
- *Lasers can potentially mitigate the efficiency droop problem !*



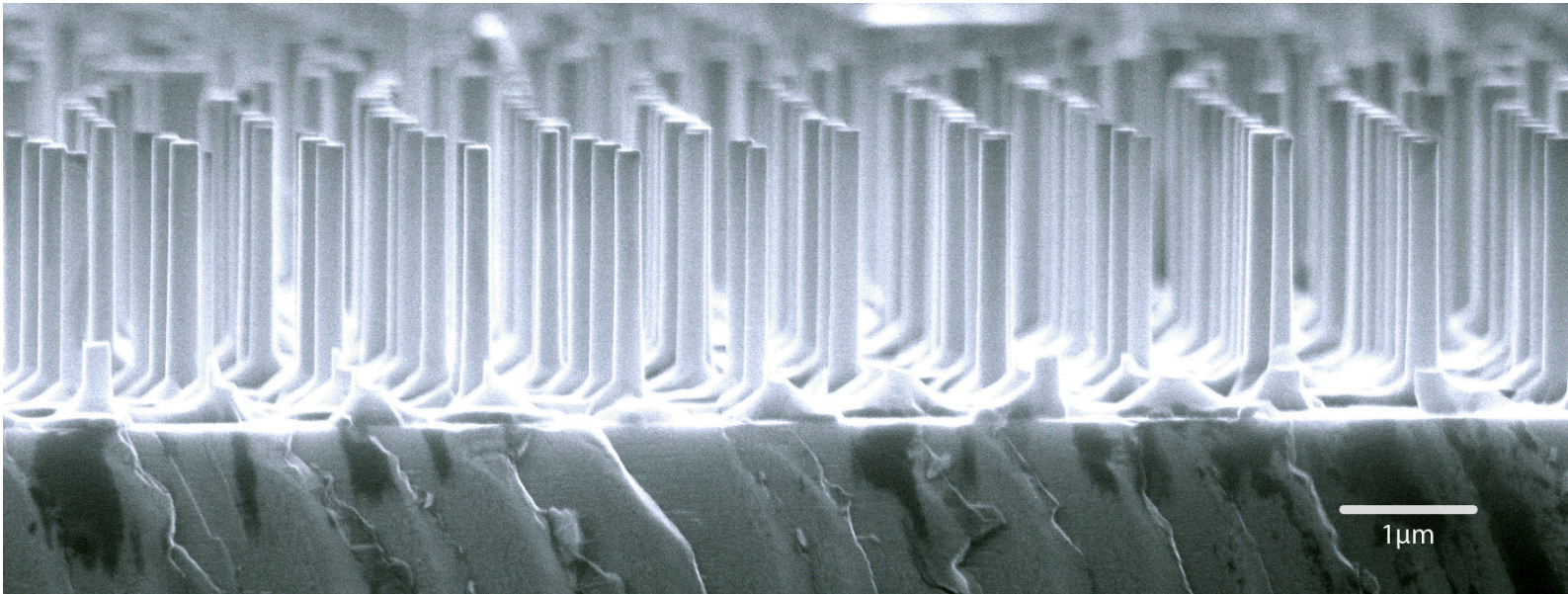
A. Neumann et al., "Four-color laser white illuminant demonstrating high color-rendering quality," *Opt. Express*, vol. 19, pp. A982-A990, 2011.

Why Nanowires for Lasing?

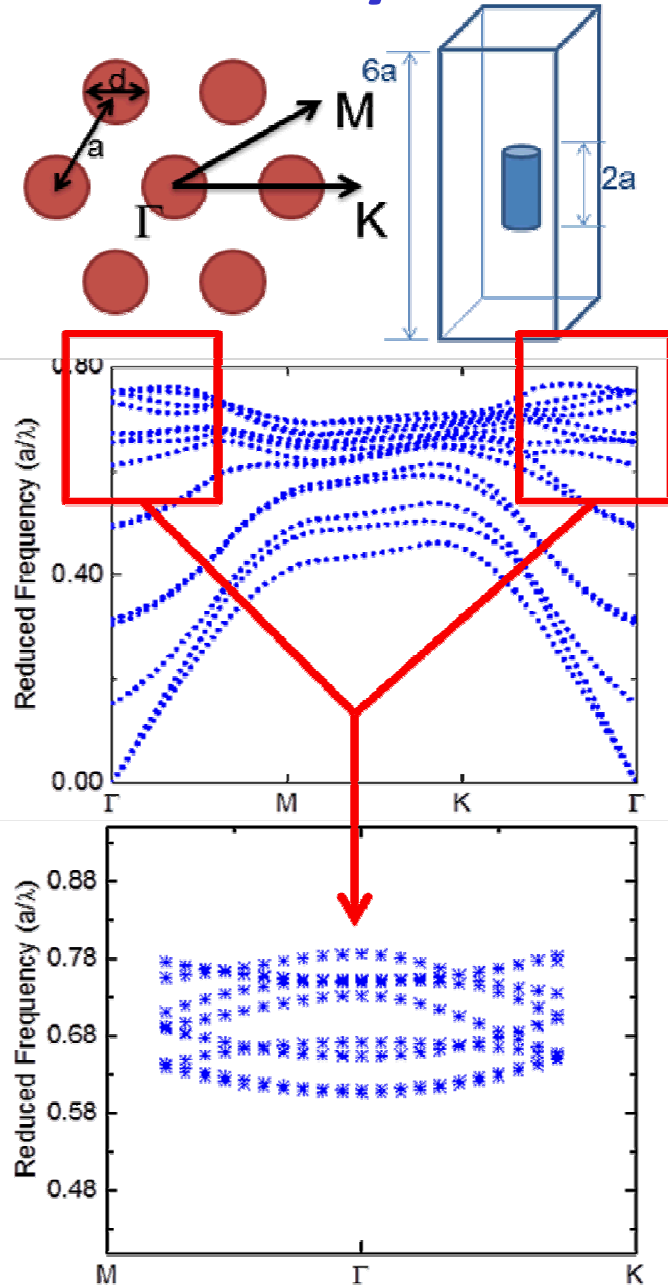
- Reduced strain
 - Greater range of alloy compositions
- Easily integrated into two-dimensional arrays



M. Krames, Philips Lumileds



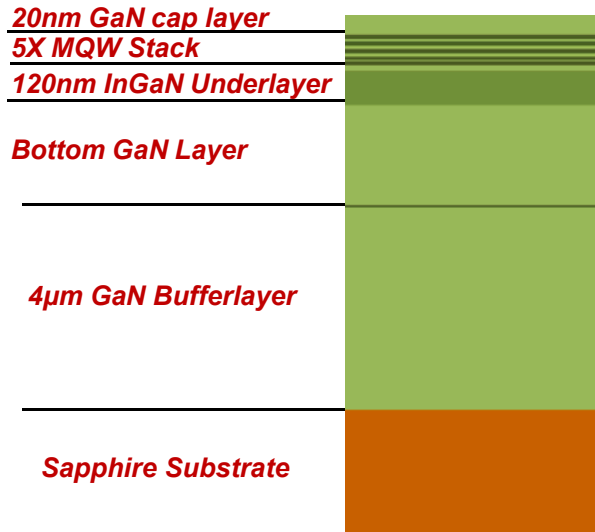
Vertically emitting photonic crystal lasers - Theory



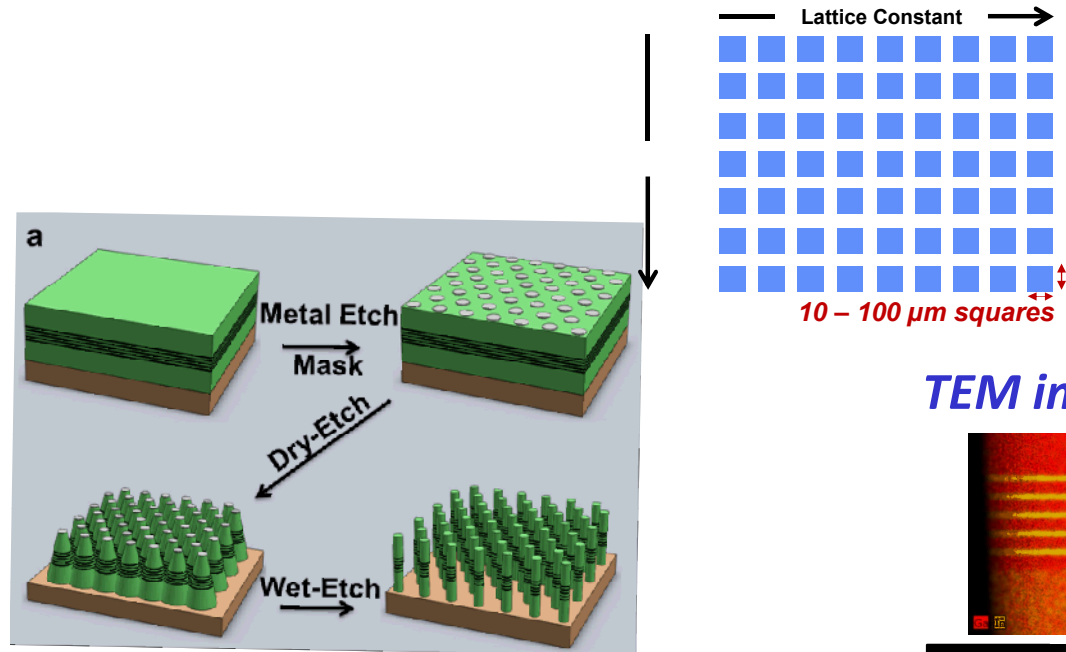
- **Low lasing threshold**
 - Increase interaction of light with the gain region
 - Enabled by 'Low group velocity modes' in photonic crystal
- **Vertical Emission**
 - At higher bands there are low group velocity modes near the Gamma point
 - Near the Gamma point the in-plane wave vectors are small resulting in near-normal emission
- **Wavelength Tunability**
 - Achieved through lattice constant and nanowire diameter variation

Fabrication of III-N nanowire laser array

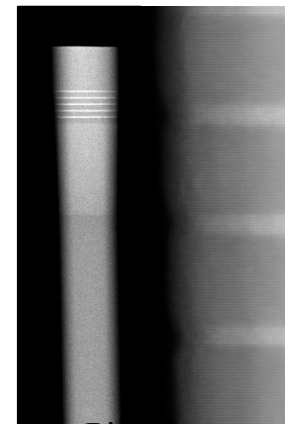
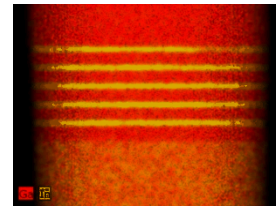
Growth of III-N active material



Patterning of 2DPC using e-beam lithography

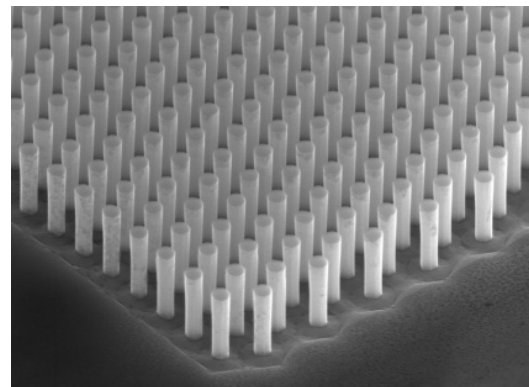
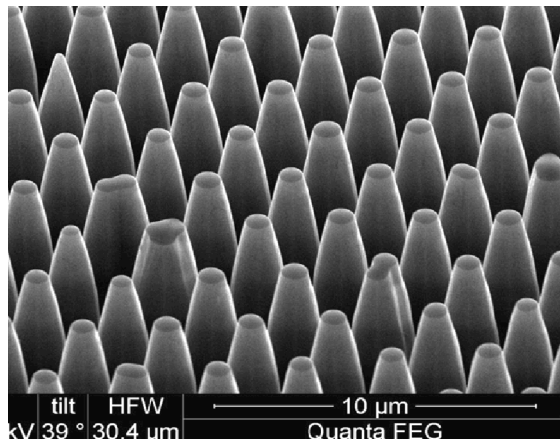


TEM images



Ping Lu,
Sandia

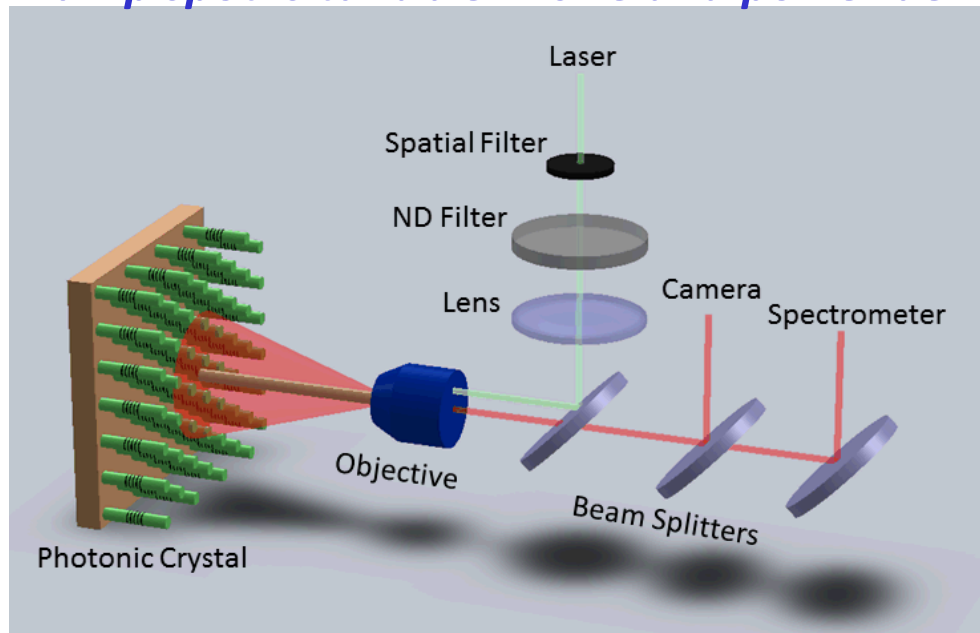
Inductively coupled plasma dry etch



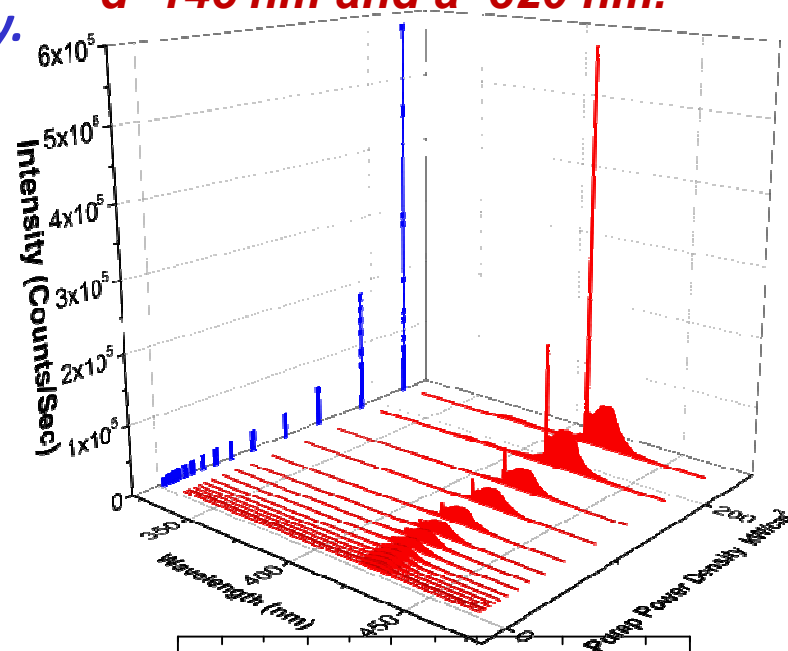
Wet etch using KOH process

Optical response – low threshold lasing

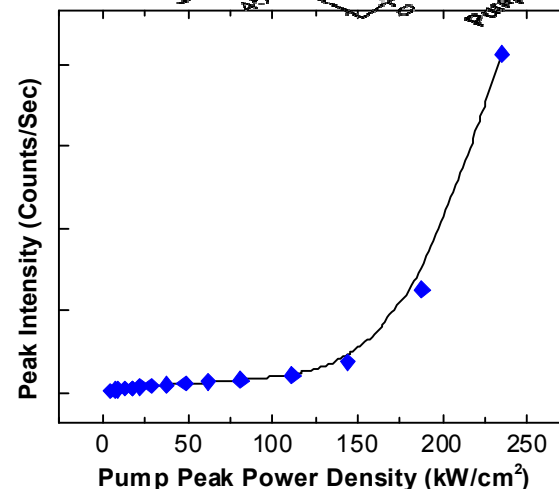
Pump spot is tunable in size and power density.



**Array Element Dimensions:
 $d=145\text{ nm}$ and $a=320\text{ nm}$.**

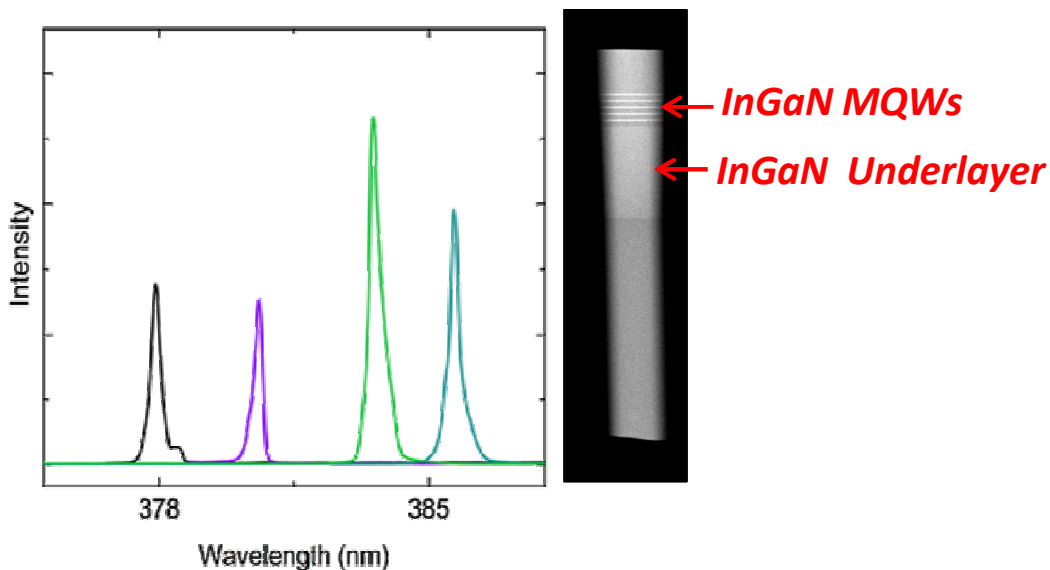


A low lasing threshold is achieved with $< 500\text{ kW/cm}^2$ for all PC lasers fabricated.

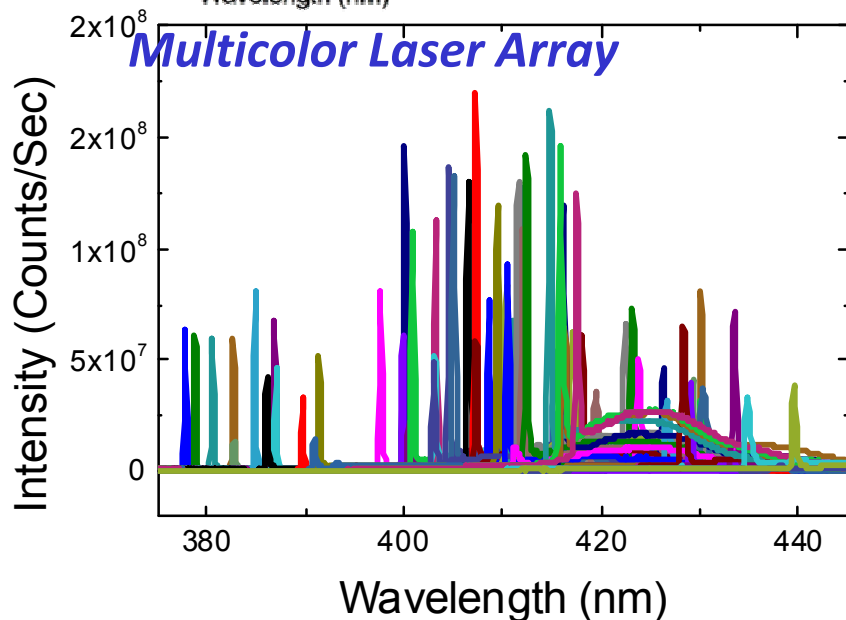


Results

Gain from multiple gain sections



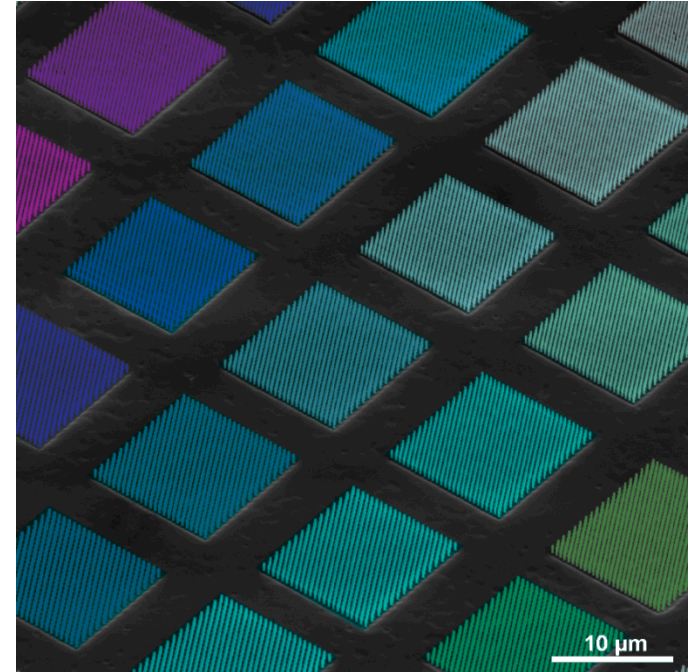
- Multiple gain regions can simultaneously lase
- Pathway for enhancing the available lasing spectral range



- Wavelength tunability (lattice constant and nanowire diameter).
- Multiple color laser emission on a single epitaxial wafer covering a spectral range from 380-440nm.

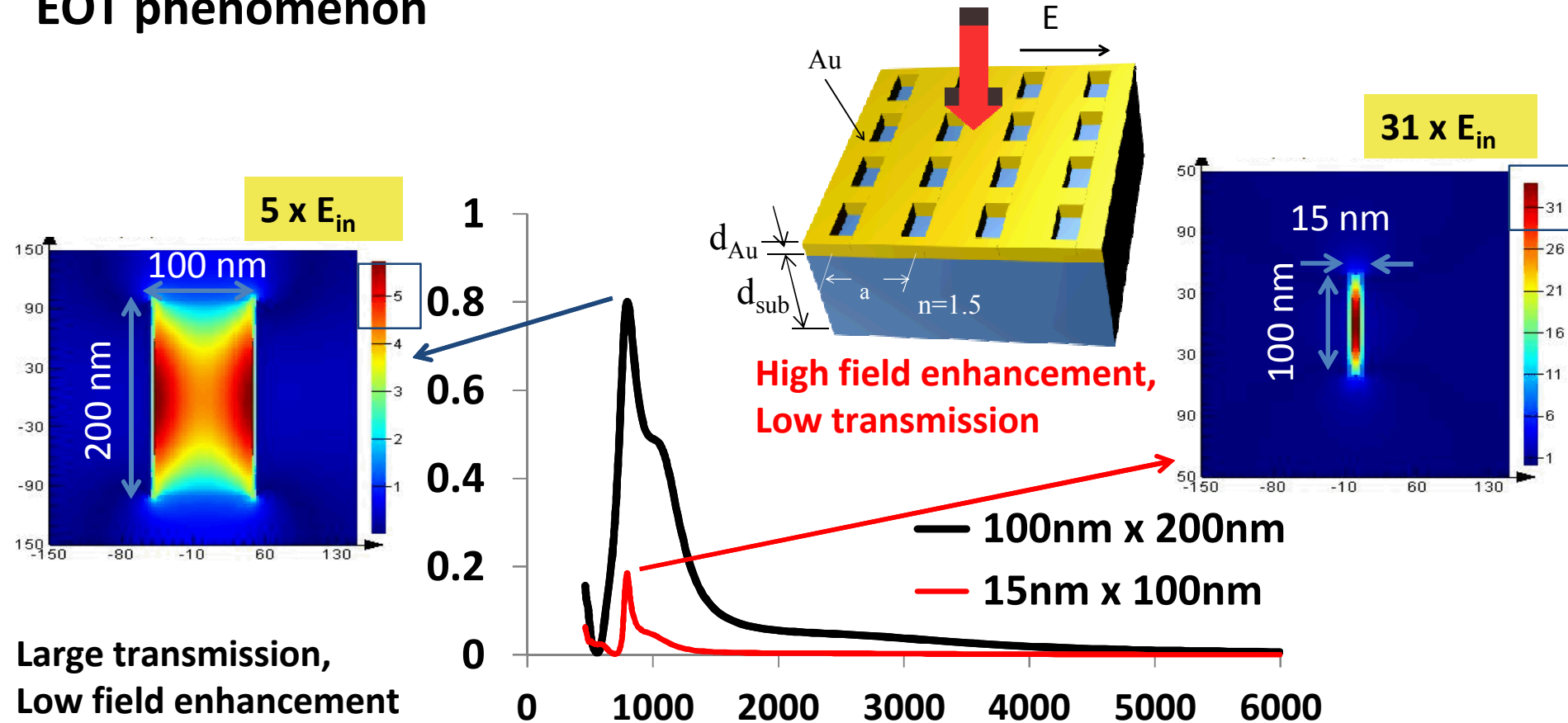
Summary and Outlook

- *Laser arrays that span a broad spectral range*
- *Near-vertical single-mode emitters*
- *Low thresholds with optical pumping with wavelength tunability*
- *Possible to fabricate high density of emitters with a larger wavelength span*
- *Potential extension of lasing spectral range all the way to the green.*
- *Significant technological implications for solid state lighting , projectors and displays.*

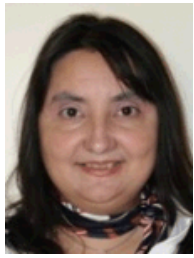


Current approach : Surface plasmon based using EOT phenomenon

Resonant



Can we achieve light confinement/field enhancement with broadband operation?

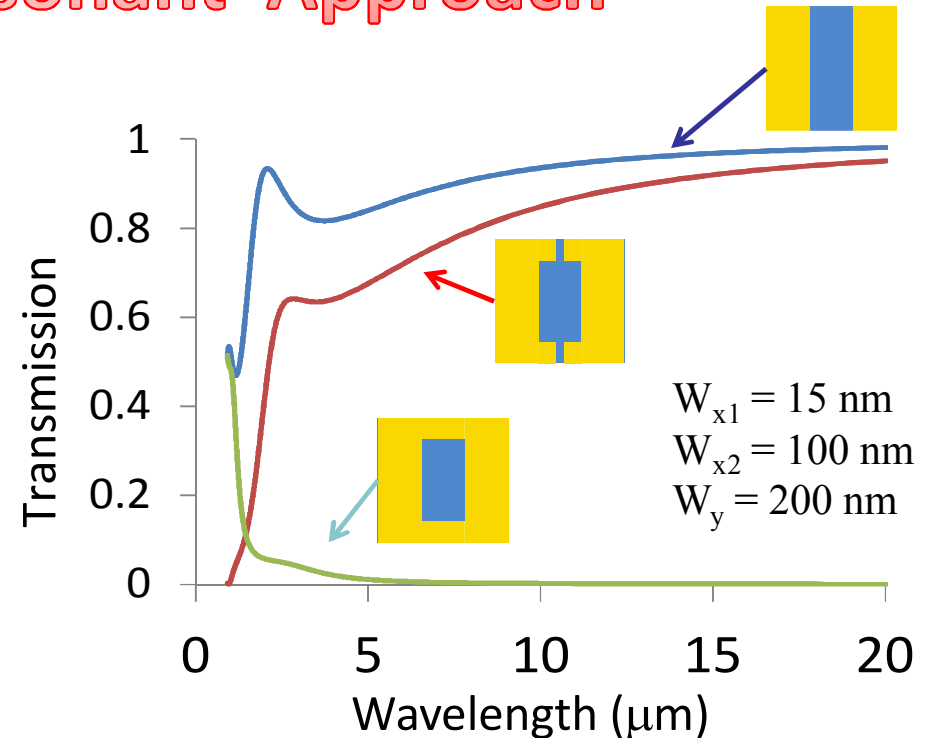
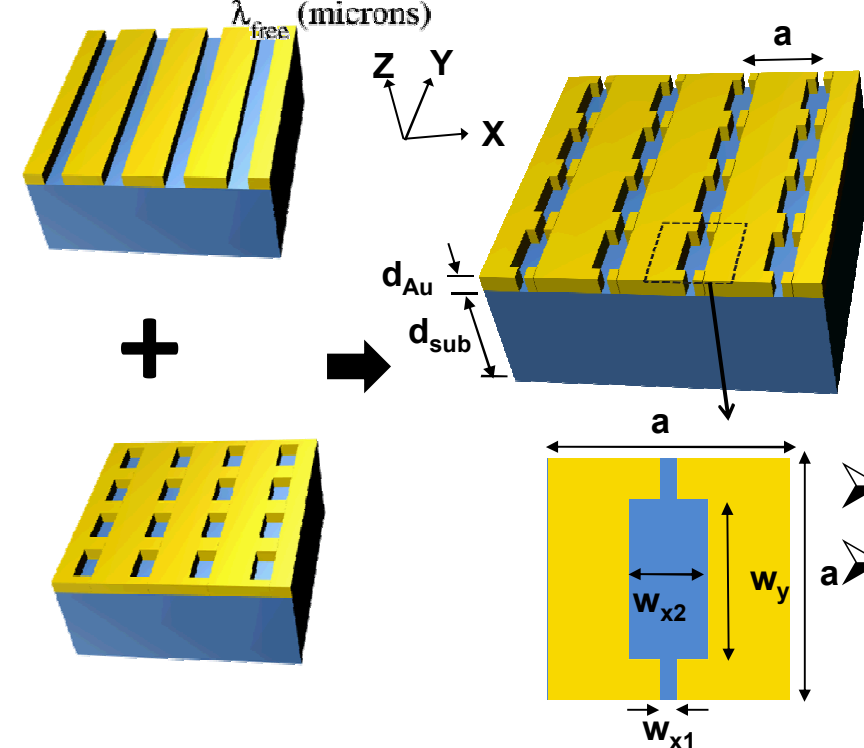
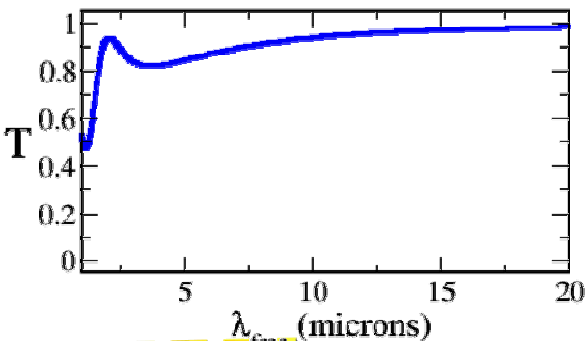


The Double-groove Structure

(In collaboration with S. Foteinopoulou- Univ. of Exeter, UK)

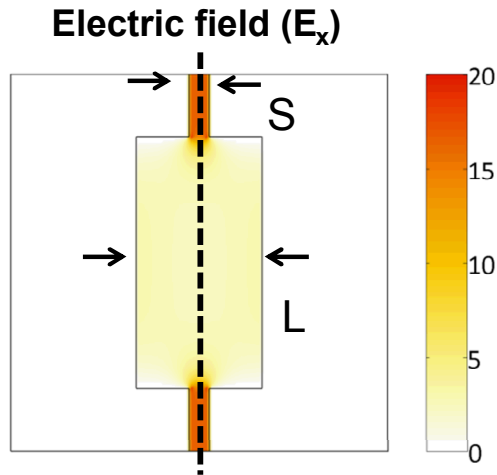
G. Subramania, S.Foteinopoulou and I. Brener, Phys. Rev. Let., 107, 163902(2011).

Non-resonant Approach

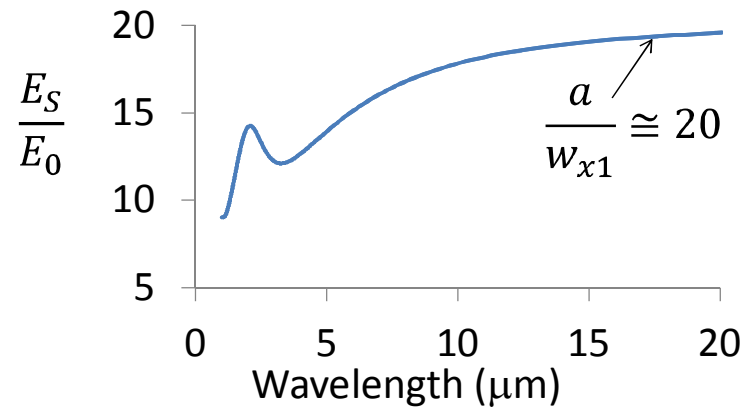


Broadband transmission
Large electric field enhancement and confinement

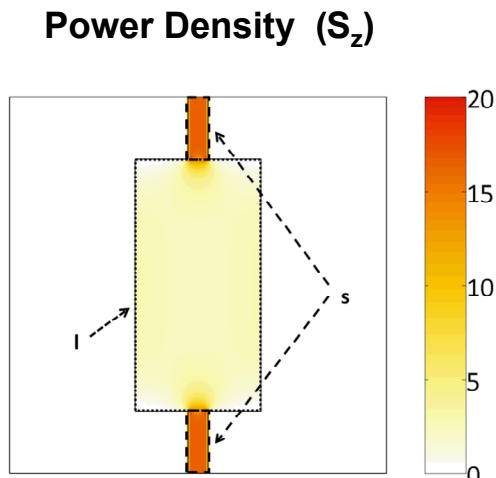
Key Results



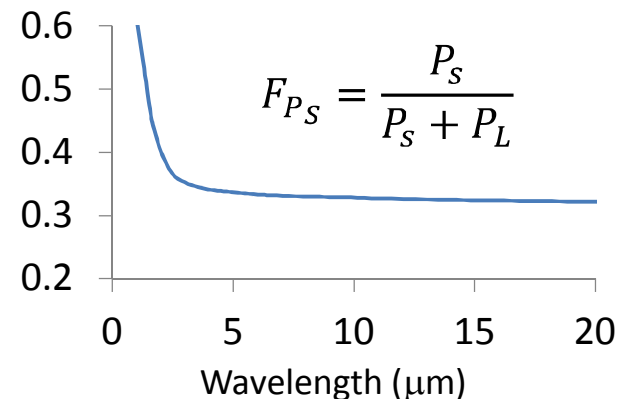
Electric field enhancement in the small gap



We can achieve large electric field enhancements in an ultra-subwavelength area ($\sim (\lambda/250)^2$) across broadband that can be controlled via structural geometry

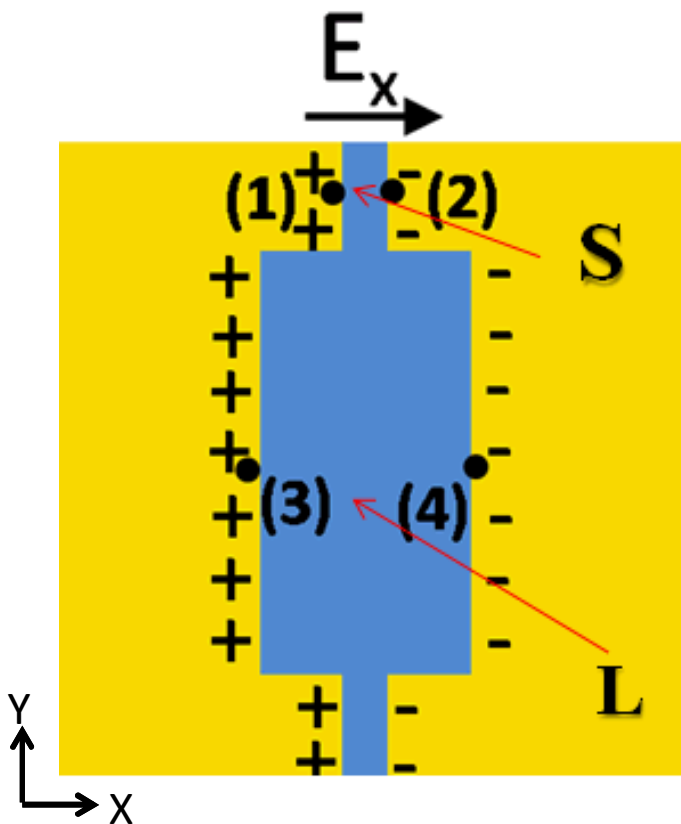


Power Fraction through the small gap



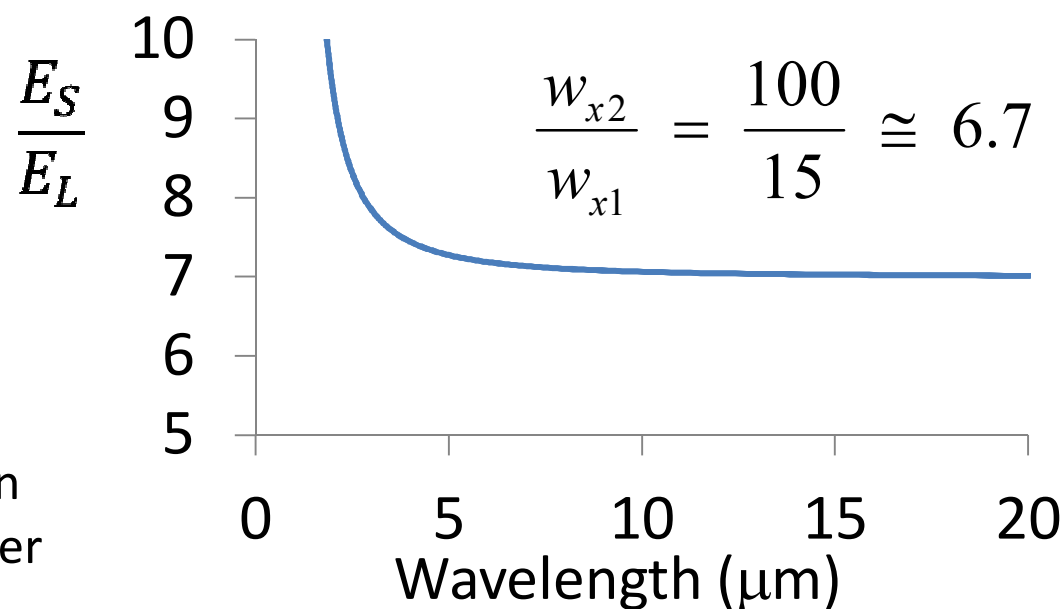
Surprisingly, nearly 30% of the transmitted power that is channeled through an area $\sim (\lambda/250)^2$ that is $1/60^{\text{th}}$ of the unit cell area.

Mechanism: Quasi-static response



- Voltage across the small and large gaps are nearly equal

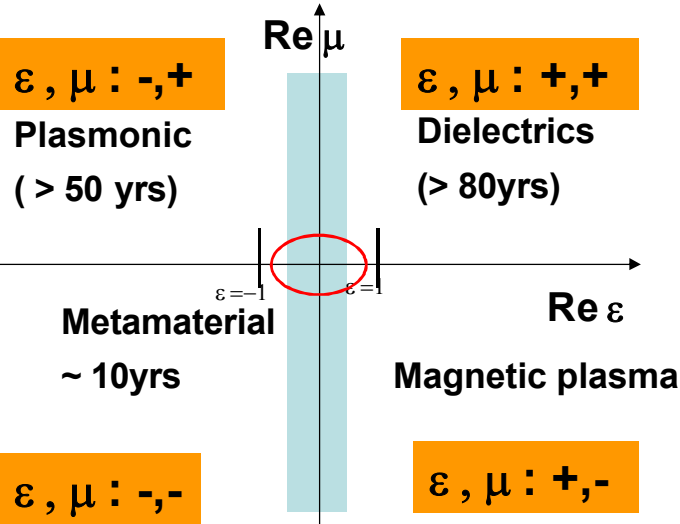
$$V_S \cong V_L \Rightarrow \frac{E_S}{E_L} = \frac{w_{x2}}{w_{x1}}$$



- Near-instantaneous response of charges even at mid-IR
- No effective current flow between small and large gap region on either side

Epsilon Near Zero Material and What Can it Impact?

Epsilon(ϵ): Dielectric constant



Epsilon Near Zero (ENZ) material is a metamaterial with unique and interesting properties.

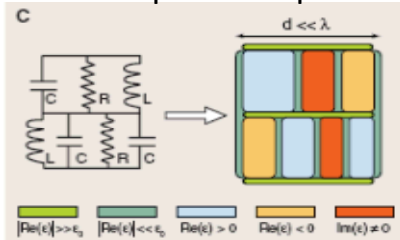
- $\underline{D} = \epsilon \underline{E} \sim 0$ for $\epsilon \sim 0$
- $V_p \rightarrow \infty$; No phase variation
- DC behavior at optical frequencies

Properties

- Sub-wavelength squeezing of light ($\lambda/20$)
- Lower loss, broadband at optical wavelengths (non-resonant, effective medium)

Optical Nanocircuits

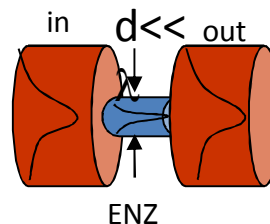
Vacuum light guiding, electrical isolation at optical frequencies



[Engheta, N., *Science* 317 1698(2007)]

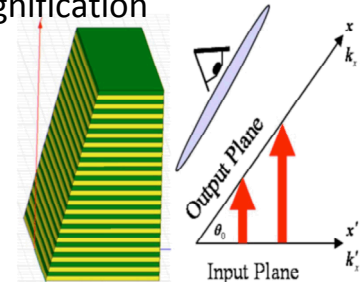
Supercoupling

Light squeezing through sub-wavelength channels



Subdiffraction Imaging

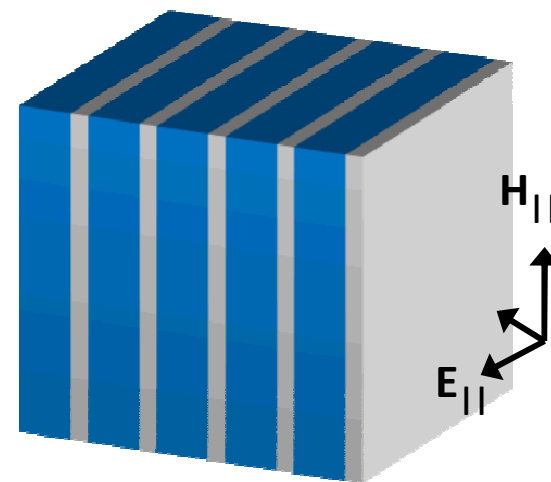
Far field subwavelength magnification



A. Salandrino and N. Engheta, *Phys. Rev. B.* 74, 075103(2006)

Effective Medium Approach to ENZ

$$\epsilon_{\text{effective}} = f\epsilon_{+}^{\text{dielectric}} + (1-f)\epsilon_{-}^{\text{metal}}$$



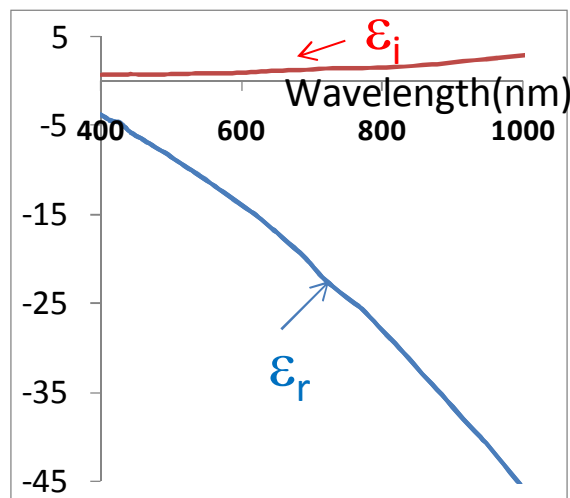
Goals

- Minimize losses due to metal
- Effective medium behavior-finer subdivision
- Reduce non-local effects – Smoother field distribution
- Easy fabricate , easy characterization

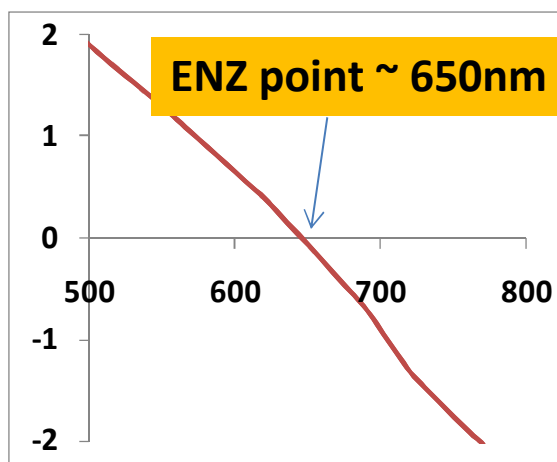
Materials Choice ϵ_{-} : Ag and ϵ_{+} : TiO_2

Ag (23%) + TiO_2 (77%)

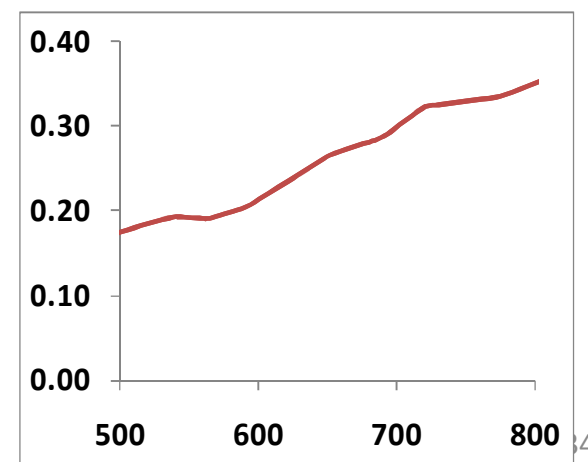
Silver(Ag)dispersion (Palik)



Composite- ϵ_{real}



Composite- ϵ_{imag}

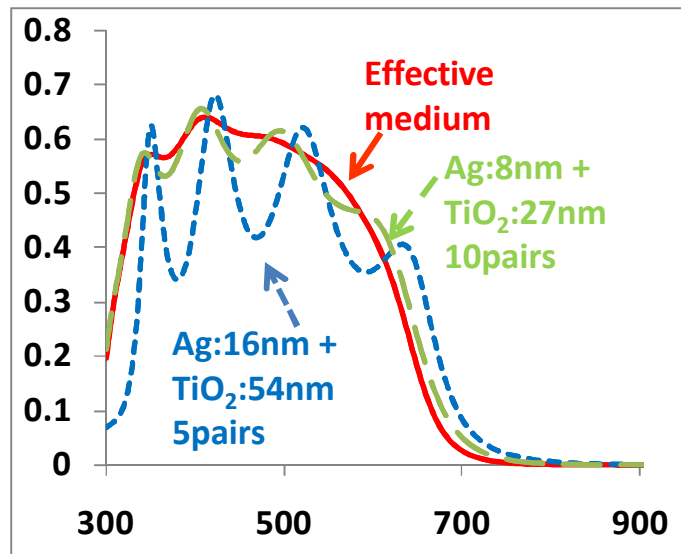


Effective Medium Multilayer Comparison

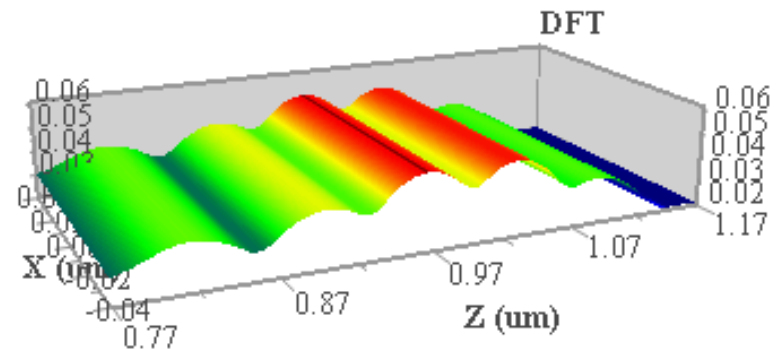
Finite Difference Time Domain Simulation



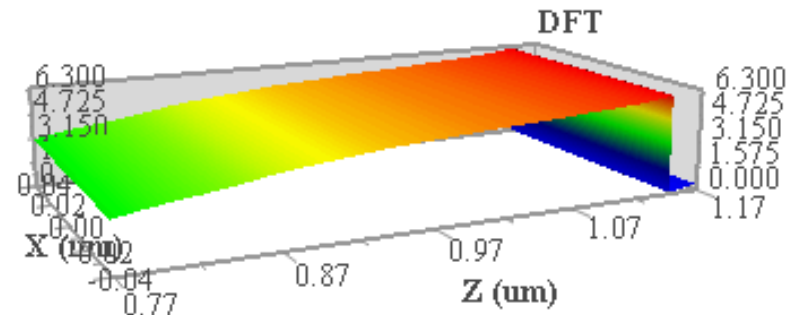
Ag/TiO₂ Composite
Ag = 16nm (23%); TiO₂ = 54nm (77%)



E field amplitude at ~ 653nm , ENZ point



E field phase at ~ 653nm , ENZ point

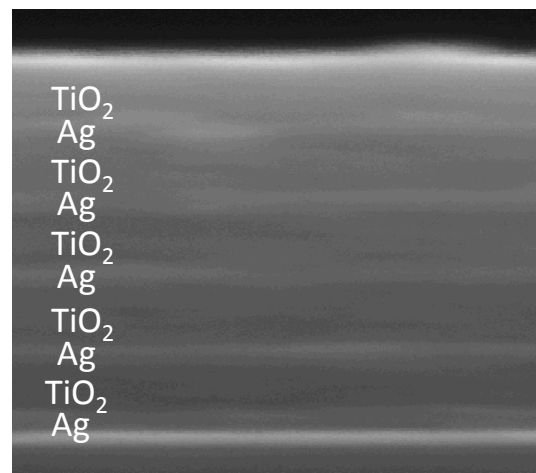
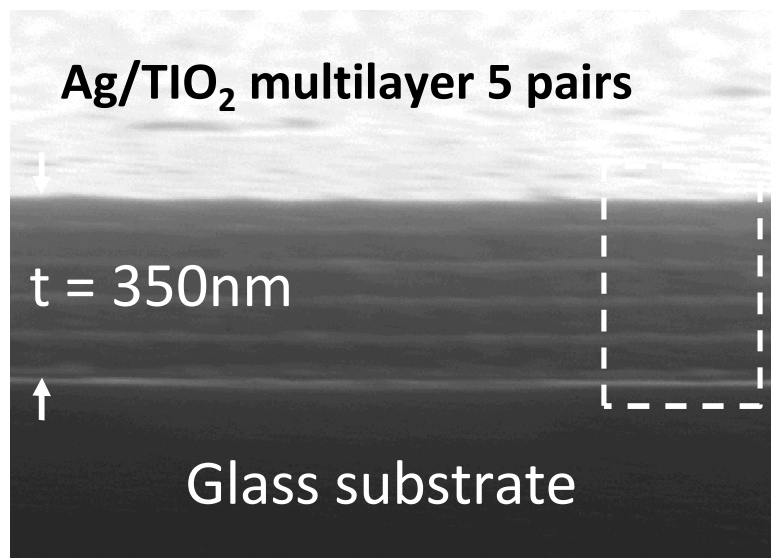
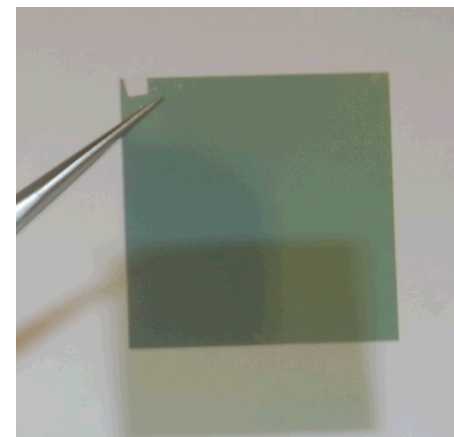
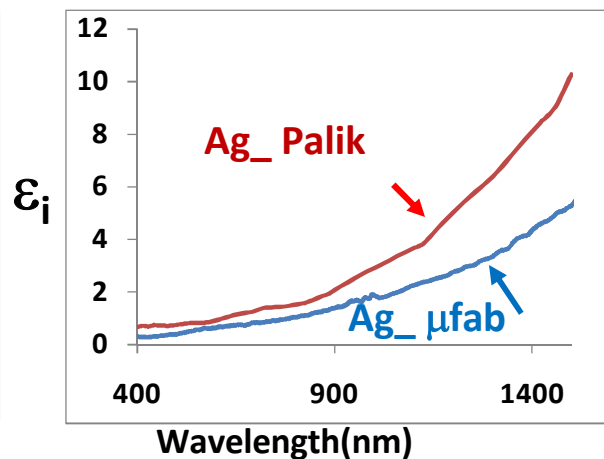
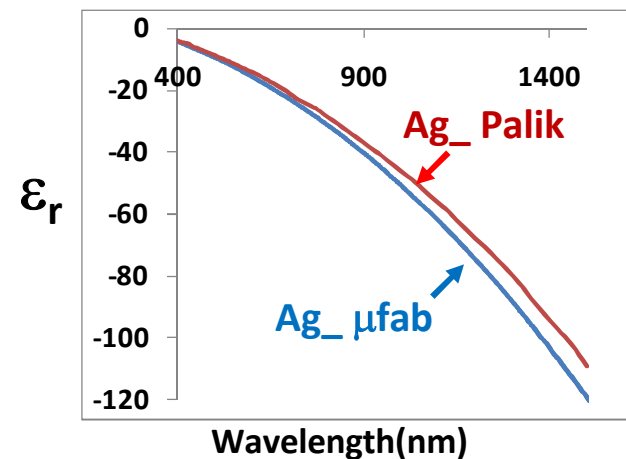


Small
Phase
Change

Ag thickness was chosen to be 16nm to obtain a continuous film using e-beam evaporation while remaining as thin as possible.

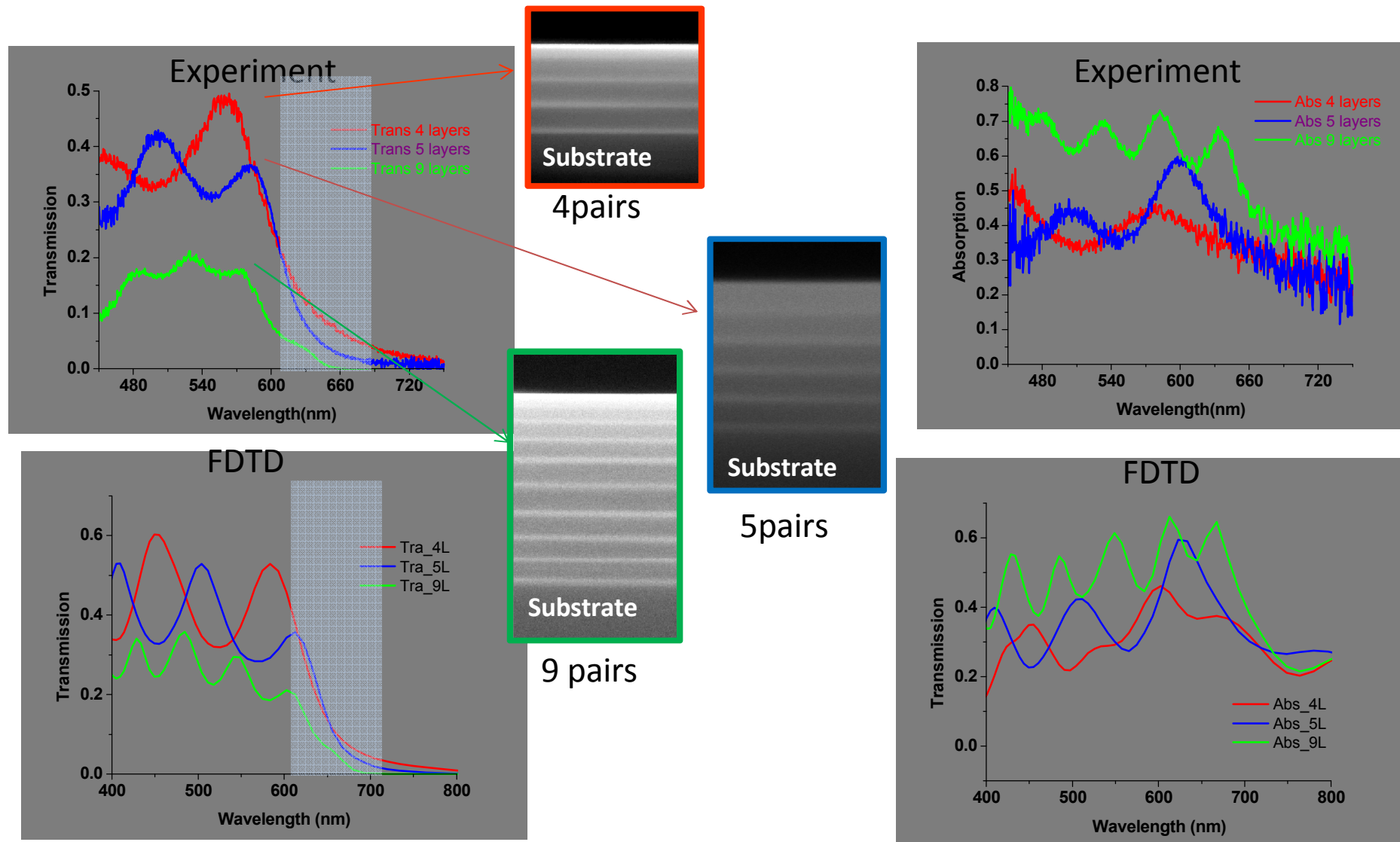
ENZ Sample Fabrication

Electron beam evaporation of alternating layers of Ag and TiO_2



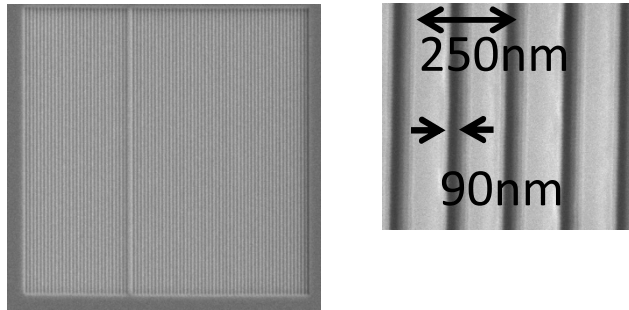
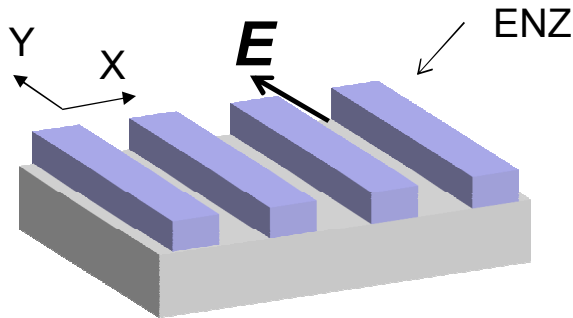
TiO_2 = 54nm
Ag = 16nm

Optical Characterization and FDTD Simulations



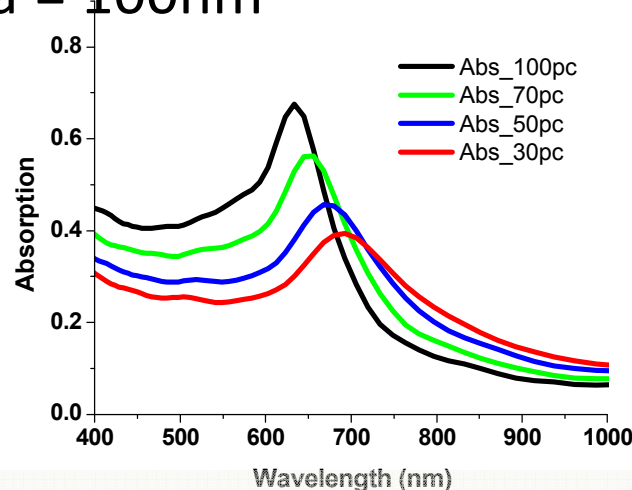
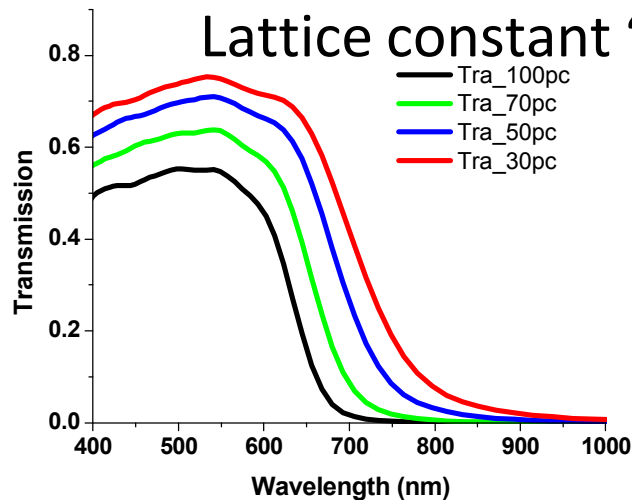
- Transmission reduces with increased number of pairs – Metal absorption
- Experimental absorption about 10% more than FDTD

Approach to Reducing Metal Absorption effects



$$\epsilon_{effective} = f \epsilon_{\text{dielectric}} + (1 - f) \epsilon_{ENZ}$$

- Light polarized along the grating
- Ideally, grating period as small as possible for effective medium
- Increased transmission
- ENZ wavelength redshifts with grating duty cycle



Grat	λ_{ENZ}	Trans
100	660	~0.1
70	690	~0.12
50	725	~0.17
30	800	~0.09

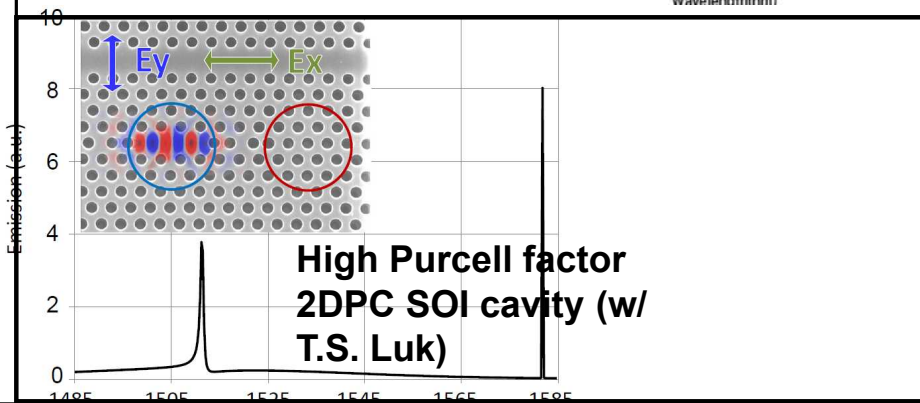
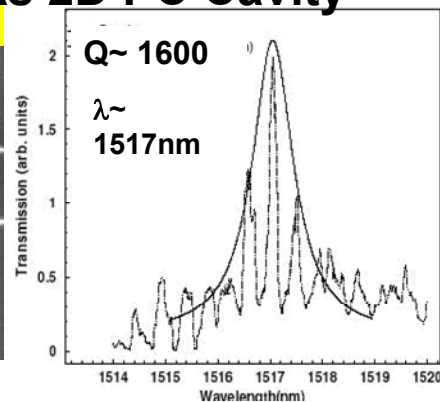
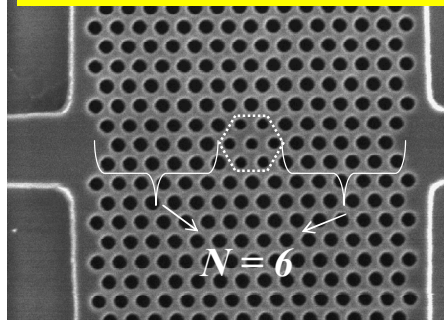
Thank you for your attention!

Backup slides

L-M Interaction in 2DPC

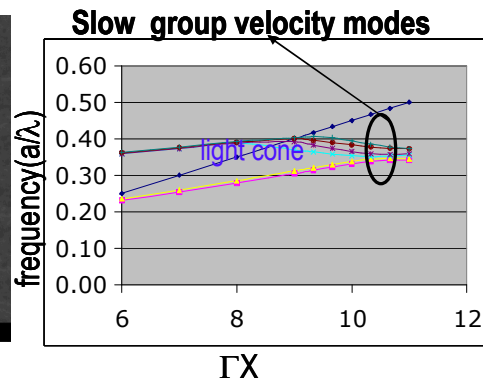
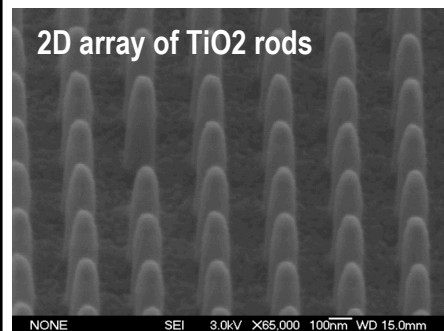
High Q GaAs 2D PC Cavity

Super-defect cavity $d' = 195\text{nm}$

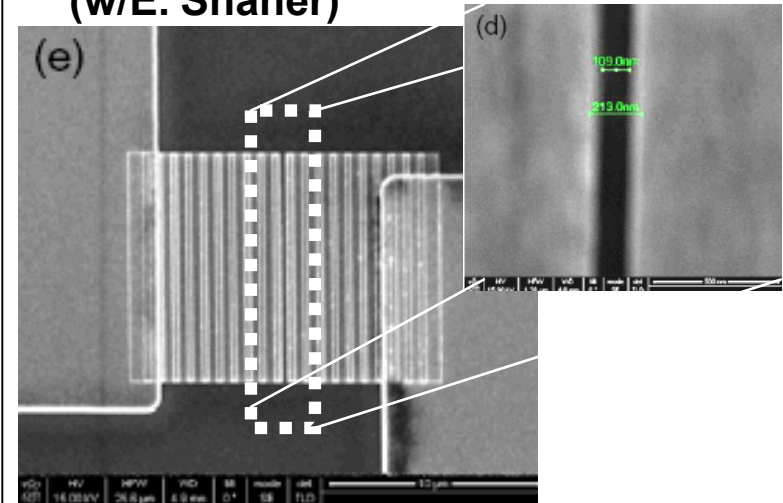


Slow group velocity mode lasing

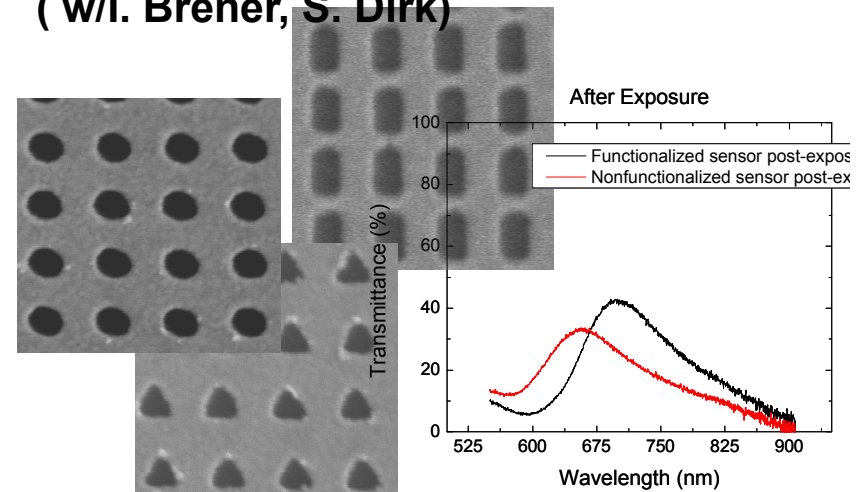
2D array of TiO2 rods



Surface plasmon Auston Switch (w/E. Shaner)



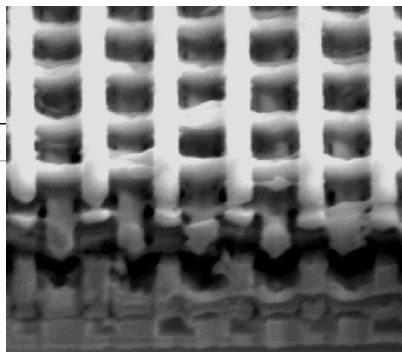
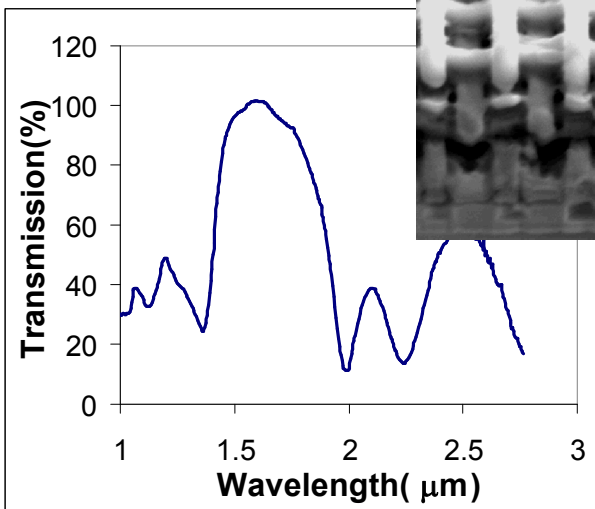
Nanohole EOT based sensors (w/I. Brener, S. Dirk)



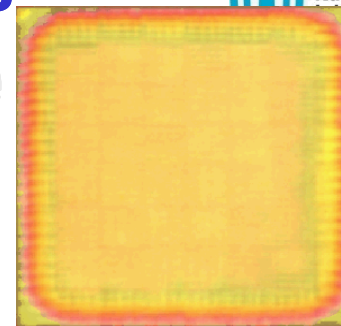
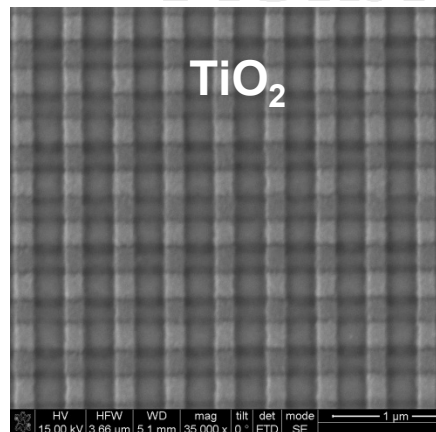
3DPCs: Wavelength, Materials

Visible

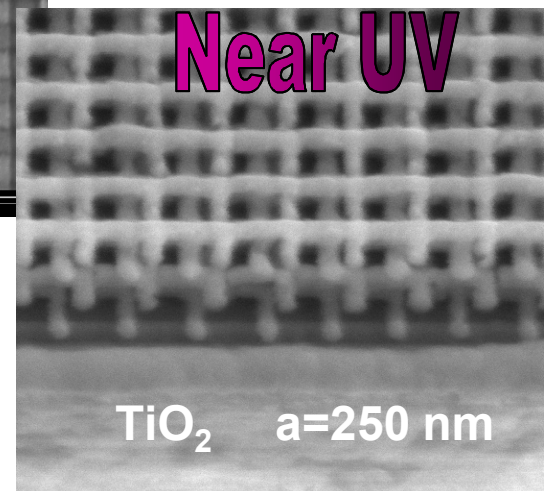
Si near-IR



TiO₂

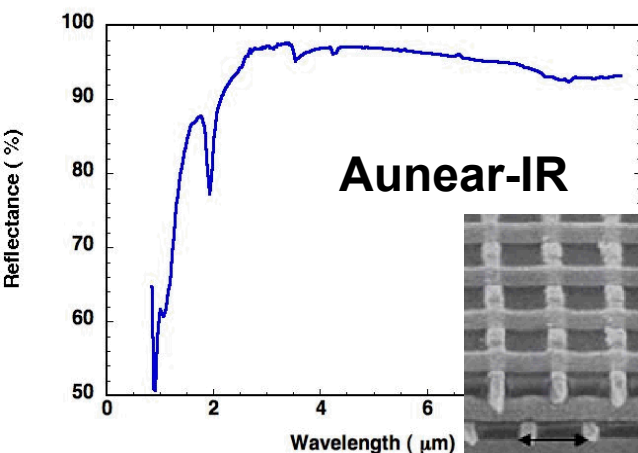


Near UV

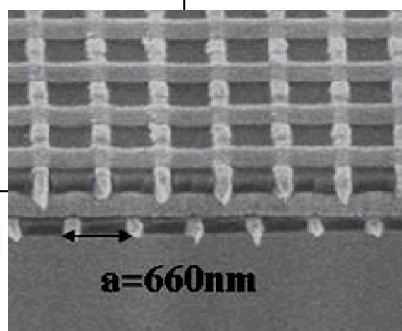


TiO₂ a=250 nm

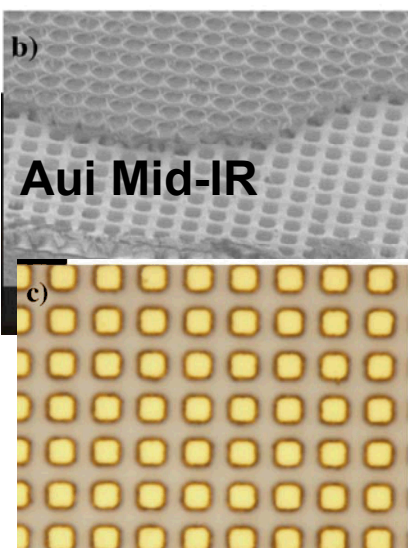
- Mid IR to Near UV
- Si, Au, TiO₂ and GaN



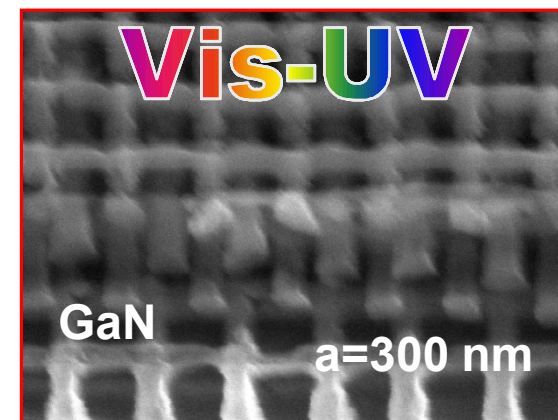
Au near-IR



a=660nm



Au Mid-IR

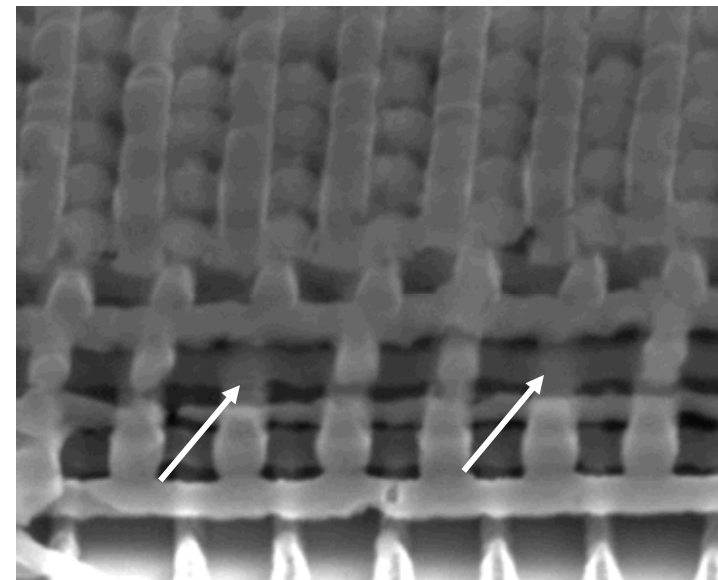
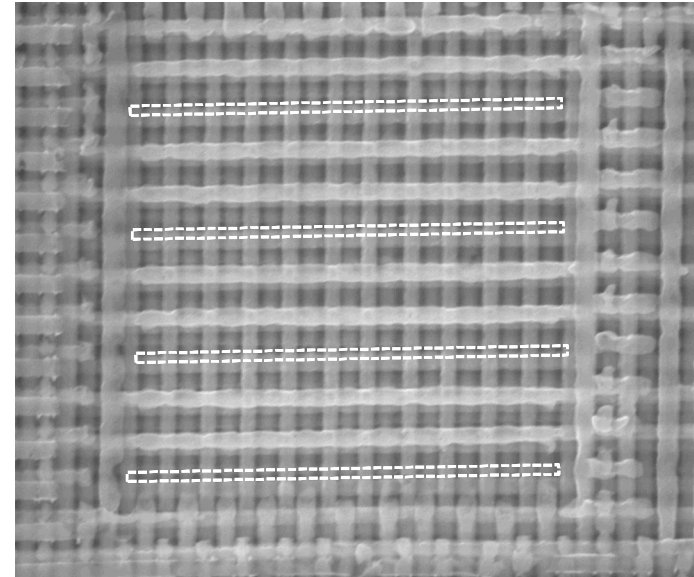
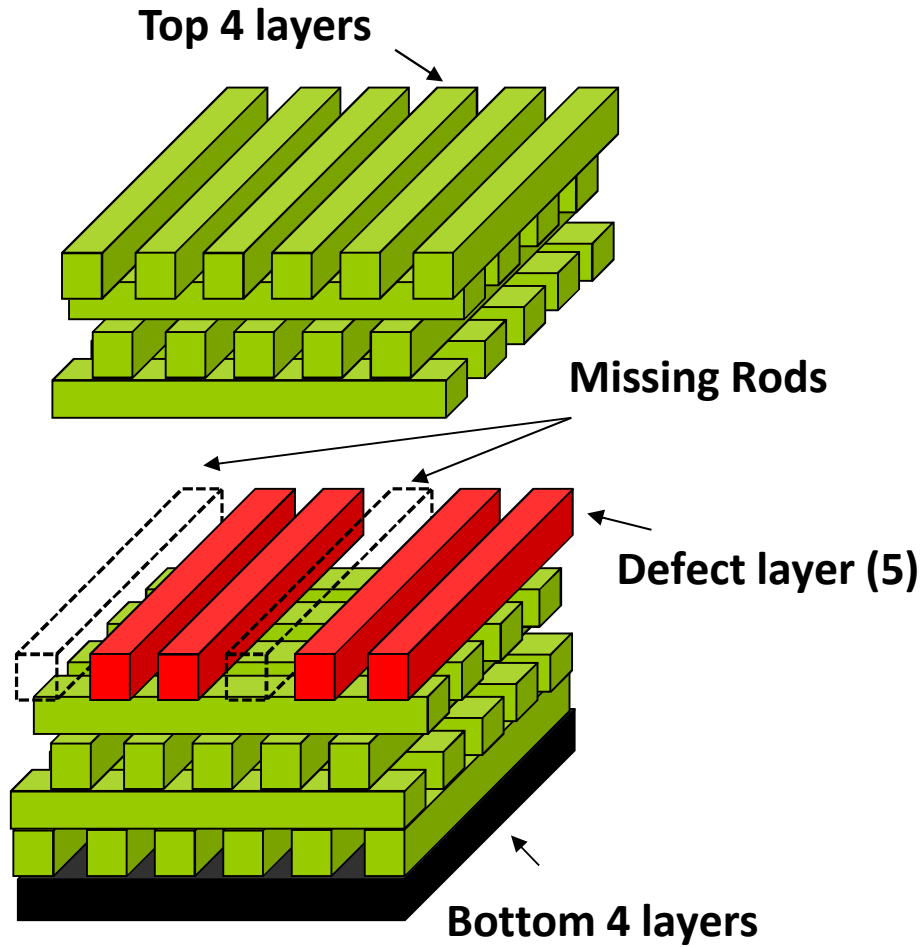


GaN

a=300 nm

Vis-UV

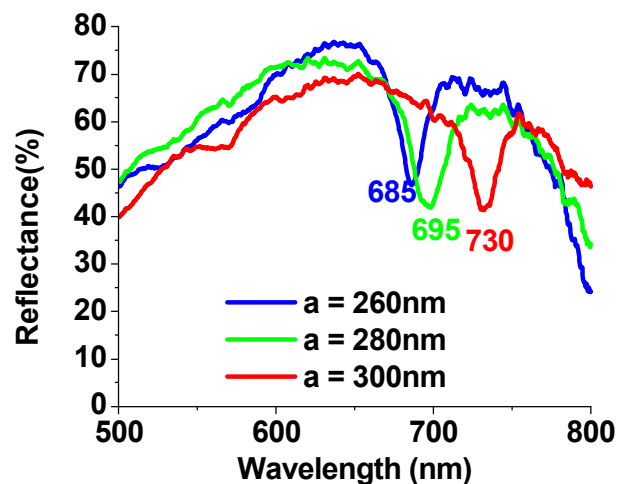
Logpile PC Cavity



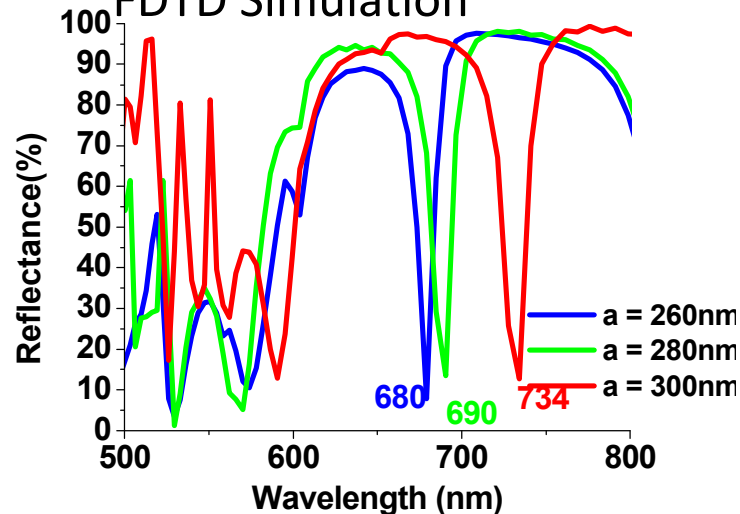
Logpile PC Cavity Optical Response

Reflection

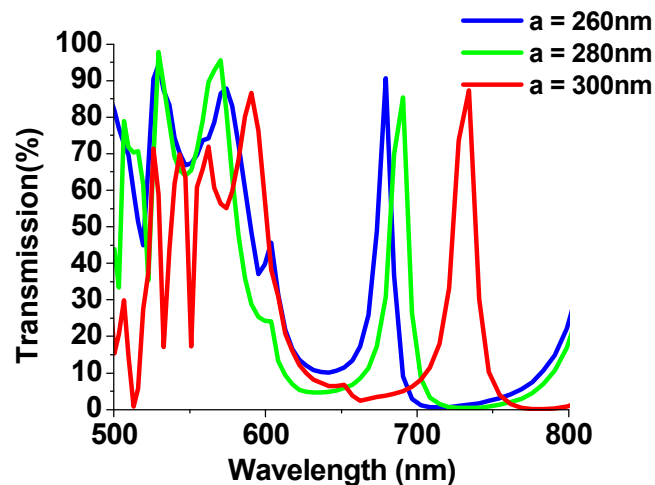
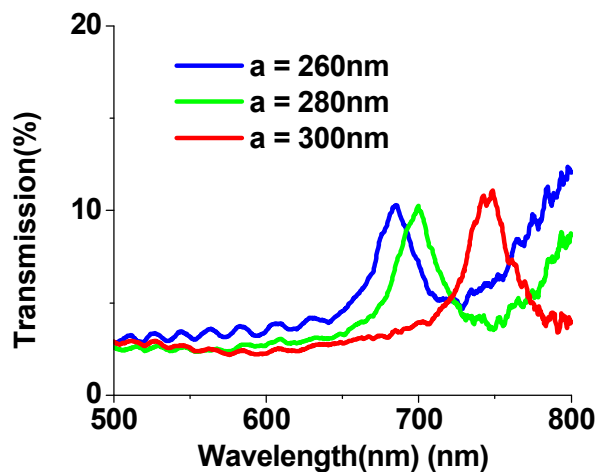
Experiment



FDTD Simulation



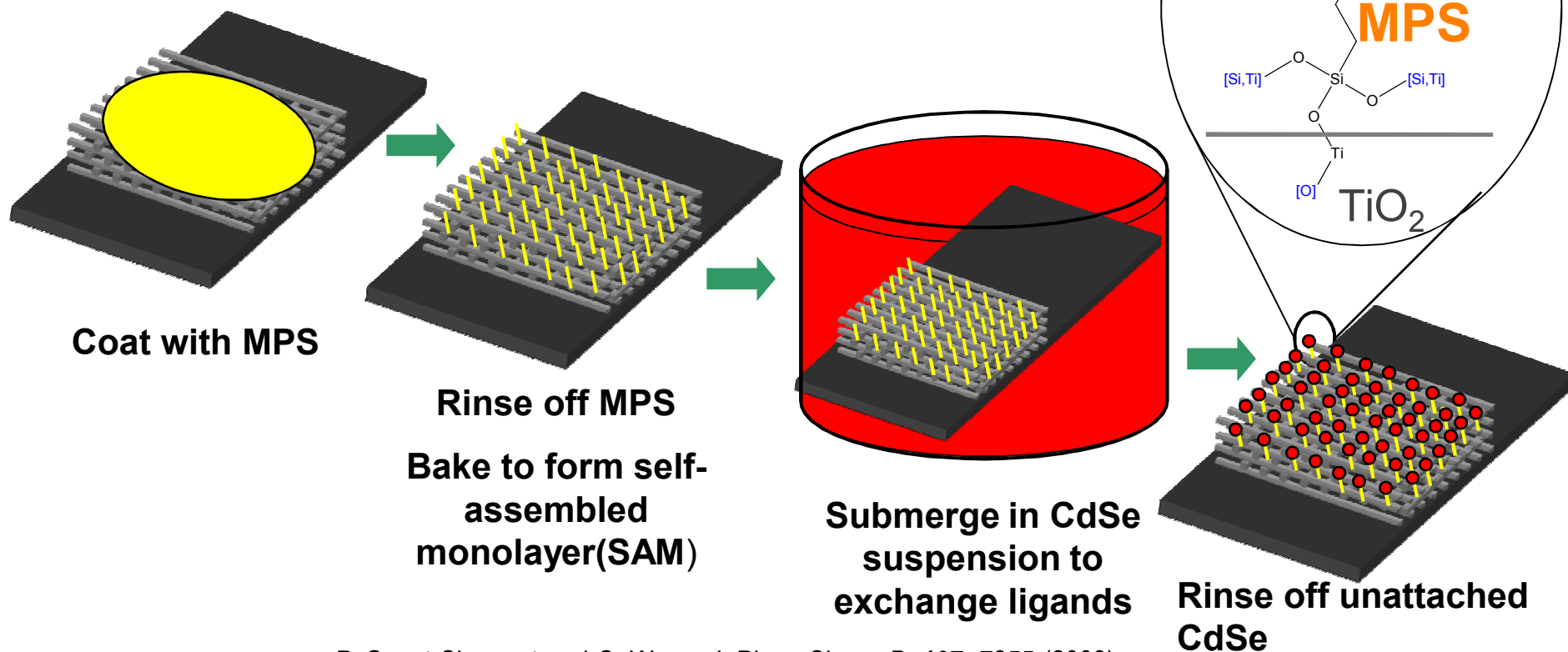
Transmission



G. Subramania et. al. , Nano Lett. **11**, 4591 (2011).

Development of Controlled Coating of CdSe Self-assembled Monolayer On TiO_2 Rods

1. Coat TiO_2 wp with neat 3-mercaptopropyltrimethoxysilane (70 °C, 3 min)
2. Rinse with chloroform
3. Bake wp on hot plate to form linkage (120 °C, 30 min)
4. Place TiO_2 wp in TOPO-capped CdSe in toluene (RT, 1 hr)

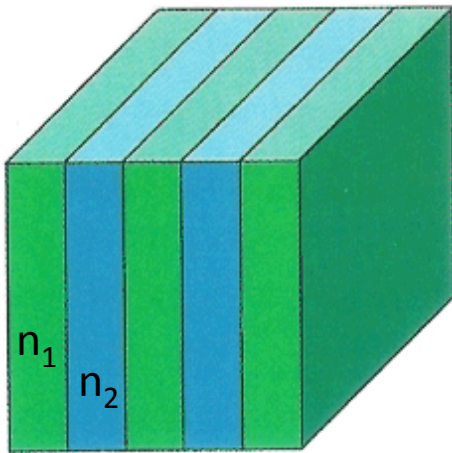


P. Guyot-Sionnest and C. Wang, J. Phys. Chem. B, **107**, 7355 (2003)

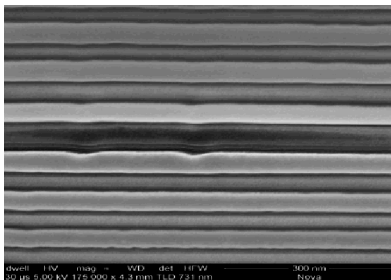
J. Pacifico, D. Gomez, and P. Mulvaney, Adv. Mater. **17**, 415 (2005)

Periodic Sub-wavelength Structures for EM Control: Photonic Crystals (PC)

1-D

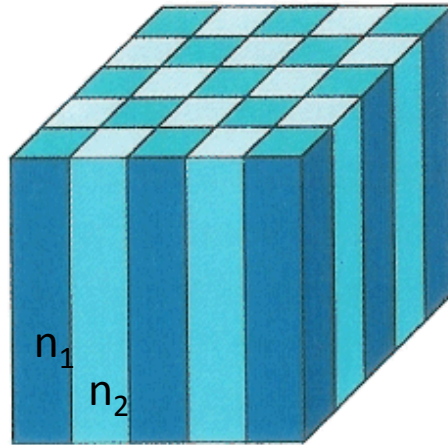


Periodic in 1 dimension

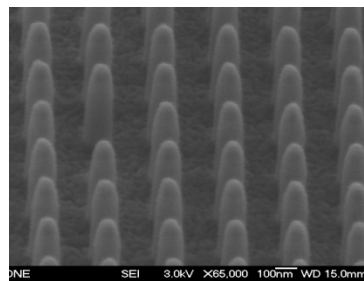


$\text{HfO}_2/\text{SiO}_2$ DBR cavity

2-D

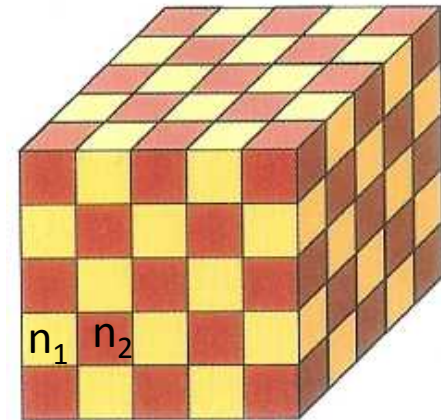


Periodic in 2 dimensions

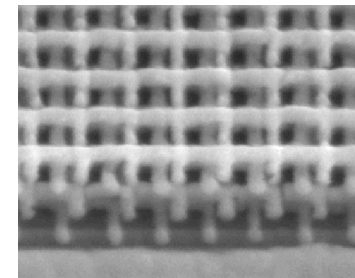


Array of TiO_2 rods

3-D



Periodic in 3 dimensions



TiO_2 logpile PC

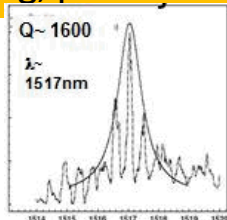
Reference: "Photonic crystals: Molding the flow of light", J.D. Joannopoulos, R.D. Meade, J. Winn, Princeton Univ.Press, NJ(1995)

Nanophotonics Activity

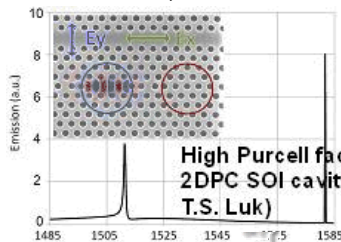
Integrated Photonics, Purcell enhancement, Nanoscale Lasing, strong Coupling, polariton lasing

Super-defect cavity $d' = 195\text{nm}$

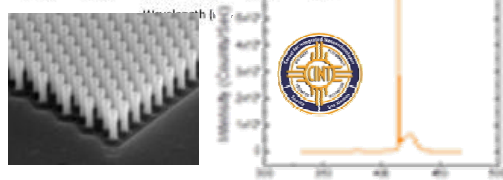
GaAs high Q 2D PC Cavity



G. Subramania, et.al. APL 85 4431 (2005)

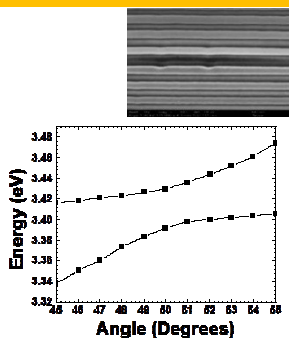
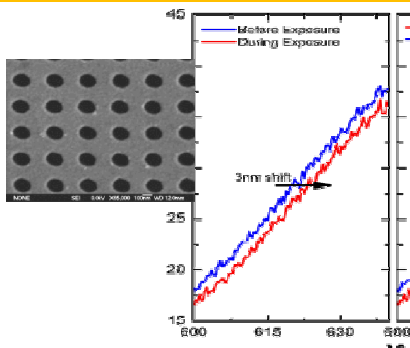


T.S. Luk et.al., JOSA-B 28, 1365



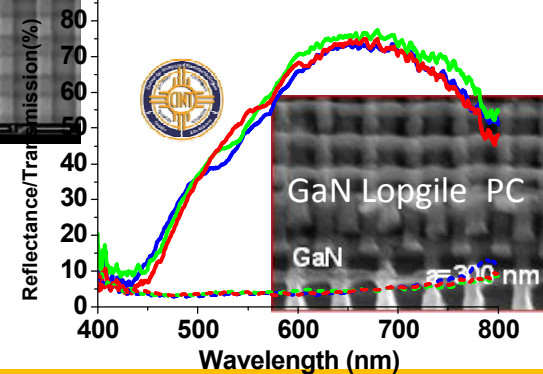
GaN 2DPC laser w/ G. Wang, I. Brener

Ultrasubwavelength light control, detection, sensing, nanocircuitry



TiO₂ Logpile visible PC

(w/ G.Wang, A. Fischer, D. Koleske)



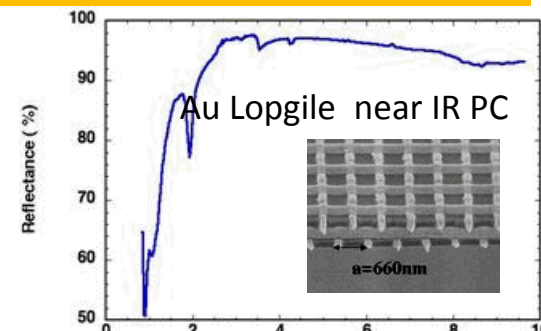
GaN Logpile PC
GaN
 $a = 300\text{nm}$

1,2D PC
3D PC
Photonic Nanostructures

Full 3D Light matter interaction control, SSL and thermal control

Metal optics and Metamaterials

Double groove Metal Nanostructure

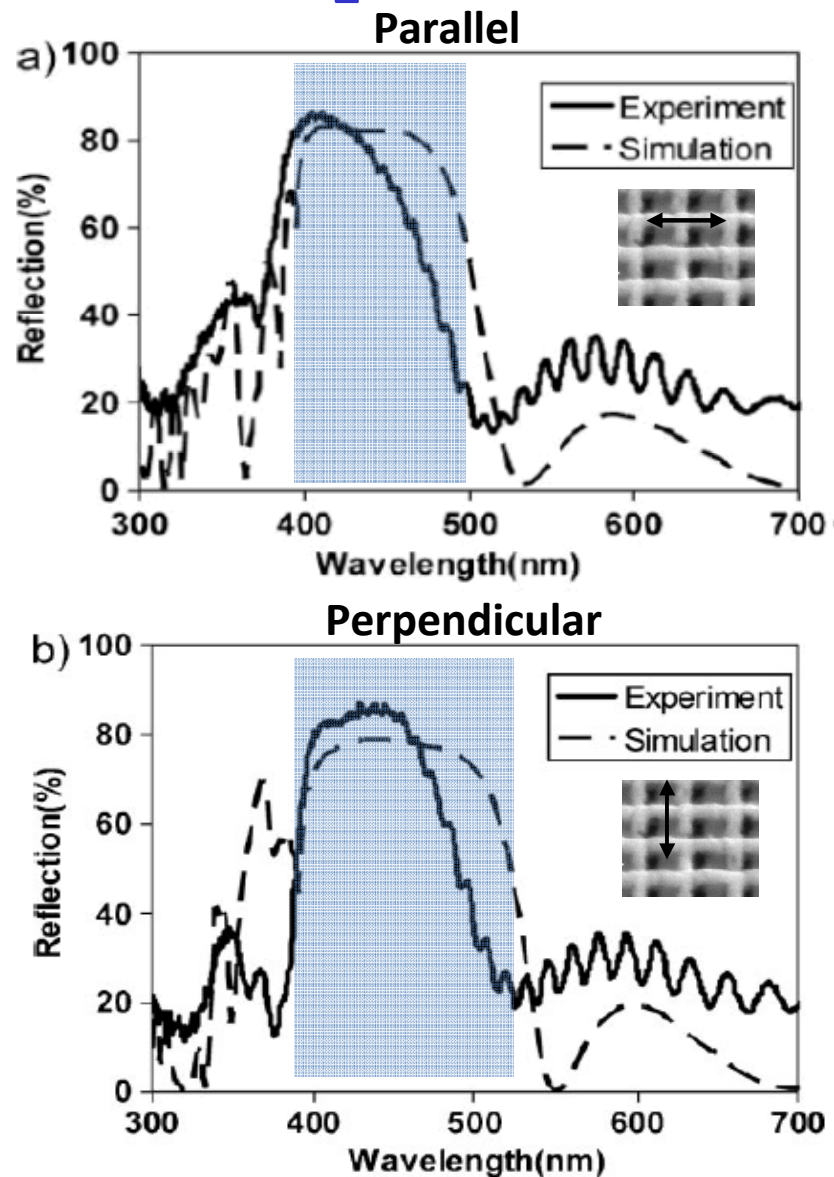
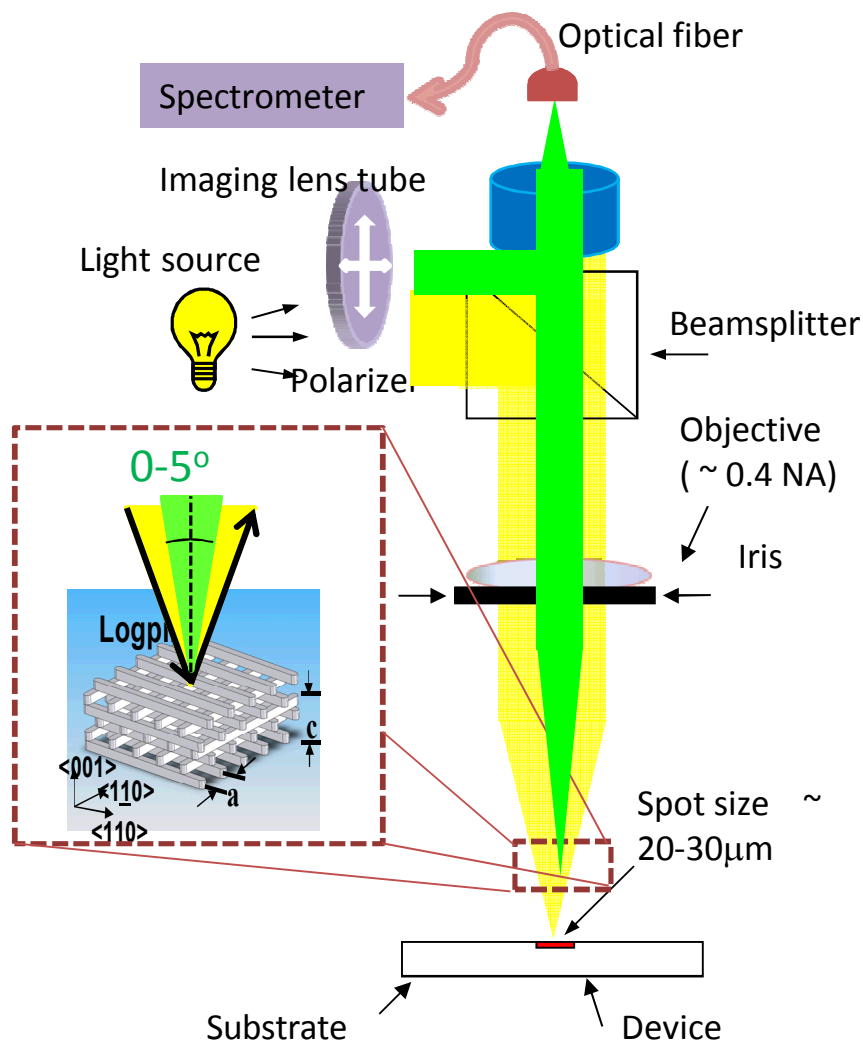


Au cubic midIR PC

TiO₂
Ag
TiO₂
Ag
TiO₂
Ag
TiO₂
Ag
TiO₂
Ag
TiO₂
Ag
ENZ Metamaterial

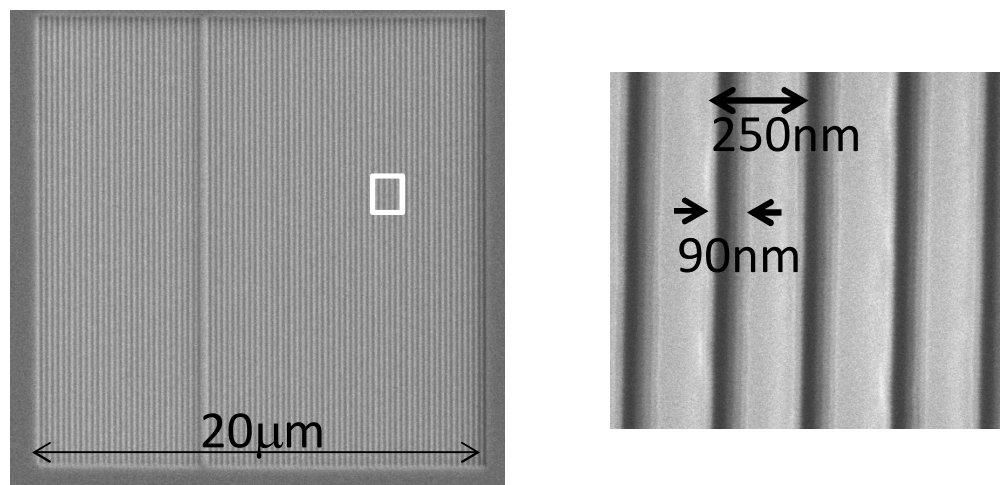
G. Subramania et.al., PRL 107 (16), 163902 (2011).

Visible- Near UV 9 Layer TiO_2 Logpile



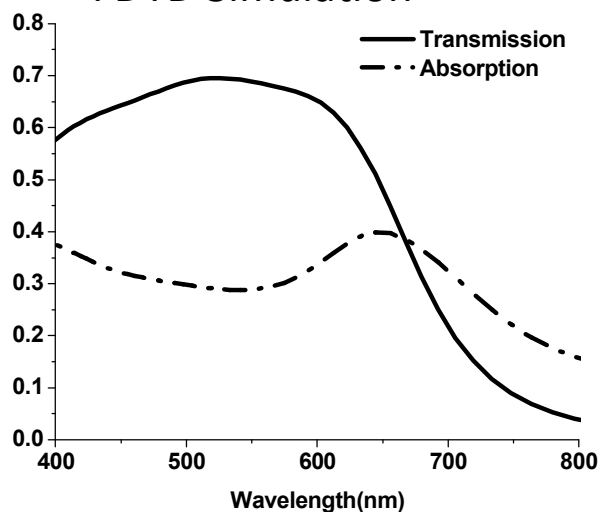
G. Subramania, Y.-J. Lee, A. J. Fischer, and D. D. Koleske, *Advanced Materials* **22**, 487-491 (2010)

Fabrication - Characterization

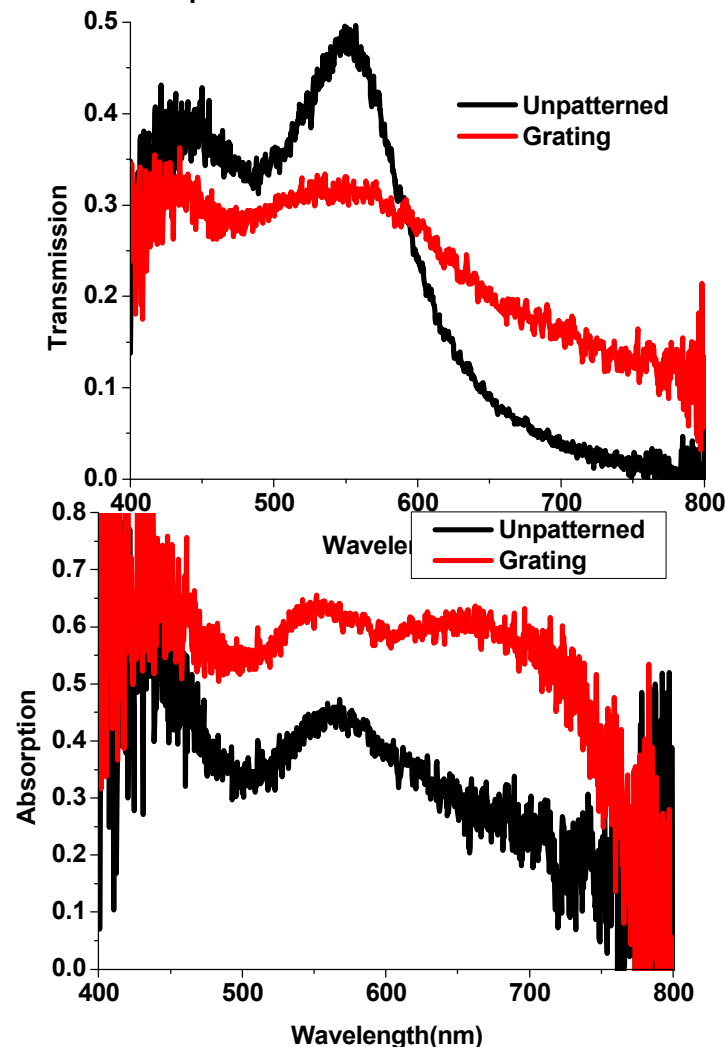


➤ Fabrication using Focused Ion Beam (FIB)

FDTD Simulation



Experiment



Band Structure Calculation

Solve Electromagnetic wave equation for Plane wave $\left\{ \begin{array}{l} E(\mathbf{r}, t) \propto e^{-i\omega t} \\ H(\mathbf{r}, t) \propto e^{-i\omega t} \end{array} \right.$

$$\nabla \times \left(\frac{1}{\epsilon(\mathbf{r})} \nabla \times \mathbf{H}(\mathbf{r}) \right) = \left(\frac{\omega}{c} \right)^2 \mathbf{H}(\mathbf{r})$$

In a periodic potential

$$\epsilon(\mathbf{r} + \mathbf{R}) = \epsilon(\mathbf{r})$$

$$\mathbf{R} = a_1 \hat{x} + a_2 \hat{y} + a_3 \hat{z}$$

Apply Bloch's Theorem

$$E, H(\mathbf{r} + \mathbf{R}) = E, H(\mathbf{r})$$

Plane Wave Expansion Method

Reciprocal (K) space

$$\varepsilon(r) = \sum_G \bar{\varepsilon}(G) e^{iG \cdot r}$$

$$E, H(r) = \sum_G \bar{E}, \bar{H}(G) e^{-i(-k+G) \cdot r}$$

Reciprocal Lattice vector

$$\vec{G} \cdot \vec{R} = 2\pi n$$

Bloch Waves $\bar{H}(G) = H_x(G)\hat{x} + H_y(G)\hat{y} + H_z(G)\hat{z}$

Eigen value equation

$$\nabla \times \left(\frac{1}{\varepsilon(r)} \nabla \times H(r) \right) = \left(\frac{\omega}{c} \right)^2 H(r)$$

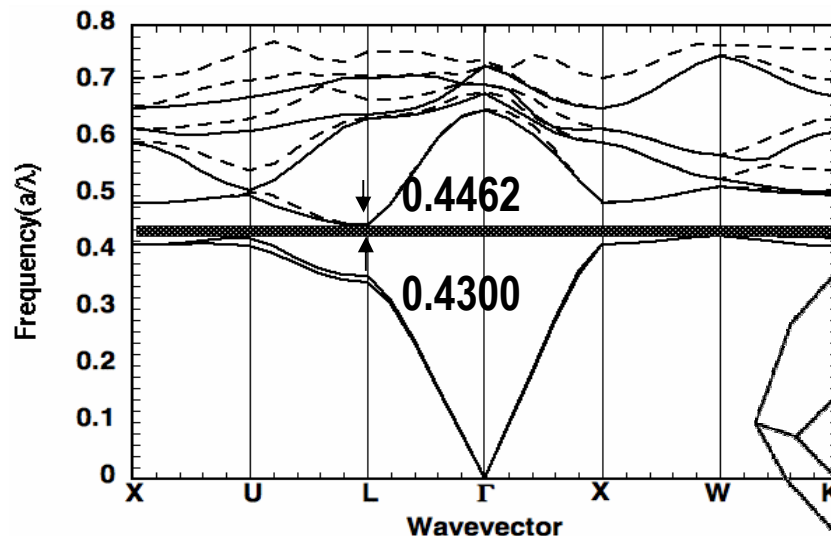


$$\mathbf{A} \bar{H}_n(k) = -\frac{a^2 \omega_n^2}{c^2} \bar{H}_n(k)$$

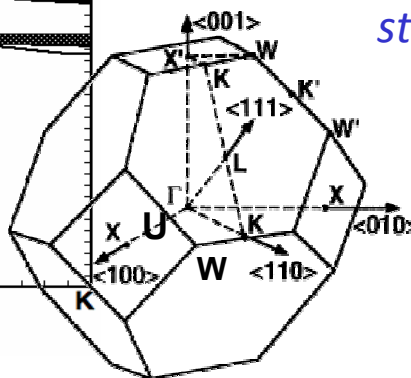
Band index

Wave vector within the first BZ

Photonic Band Structure for TiO₂ logpile



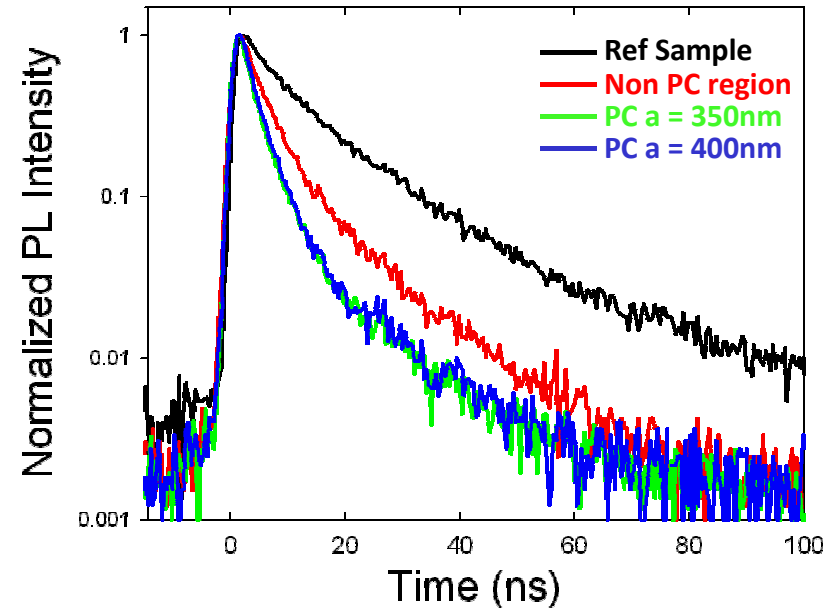
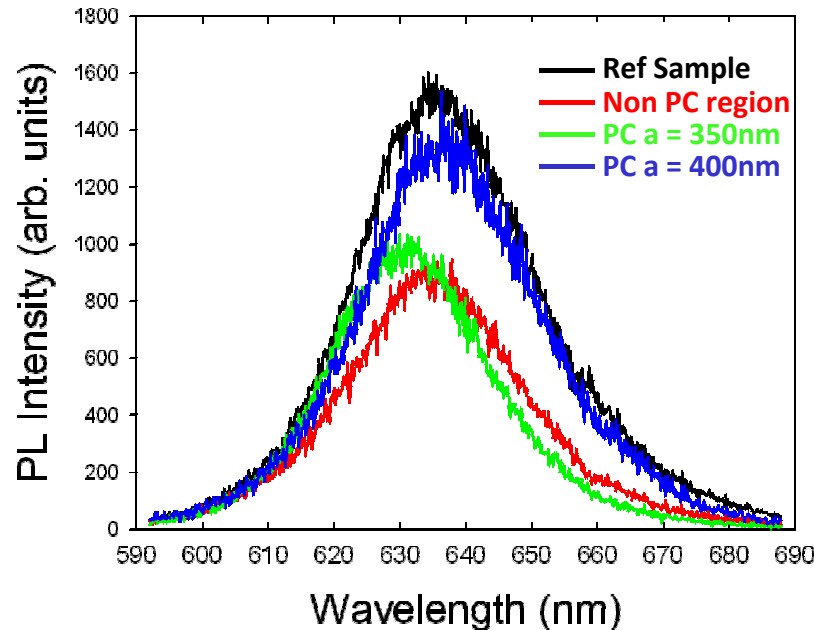
1st BZ



Eigen value equation becomes a matrix equation for which you can write a code and solve for band structure within the first Brillouin zone.

- $n \sim 2.3$
- 4% bandgap
- $\sim 20\text{nm} @ 500\text{nm}$

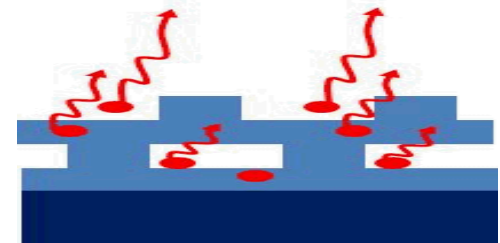
Emission Lifetime Measurements - TRPL



- Conditions: 380 nm pump, 4 MHz, 20 uW average power, 10 mm aperture
- Emitter wavelength $\sim 640\text{nm}$

- Faster lifetime in PC vs. in the reference/ no PC
- Lifetime similar for both lattice constant PCs

Ideally expect longer lifetime inside the gap (for $a = 350\text{nm}$) and shorter for outside ($a = 400\text{nm}$).



Possible reasons:

- Fewer layers of PC
- Surface QD emission